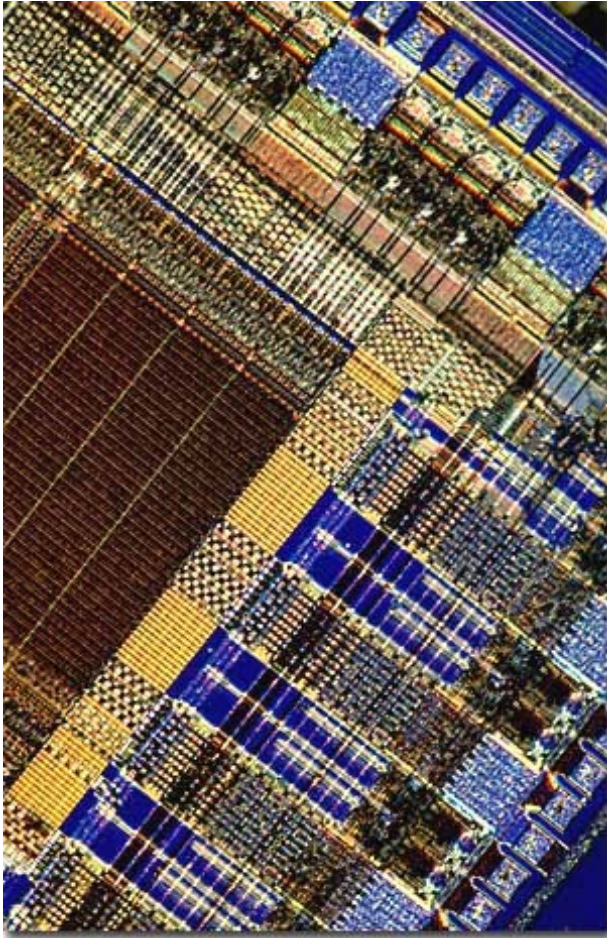


CMOS Digital Integrated Circuits



Chapter 1 Introduction

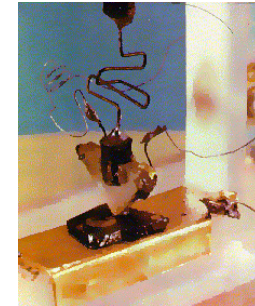
S.M. Kang and Y. Leblebici

Some History

Invention of the transistor (BJT)

Shockley, Bardeen, Brattain – Bell Labs

1947



Single-transistor integrated circuit

Jack Kilby – Texas Instruments

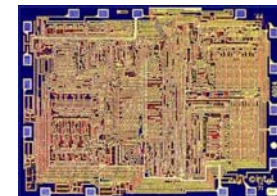
1958



Invention of CMOS logic gates

Wanlass & Sah – Fairchild Semiconductor

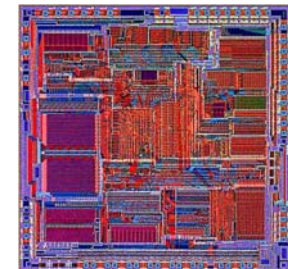
1963



First microprocessor (Intel 4004)

2,300 MOS transistors, 740 kHz clock frequency

1970



Very **L**arge **S**cale **I**ntegration

Chips with more than ~20,000 devices

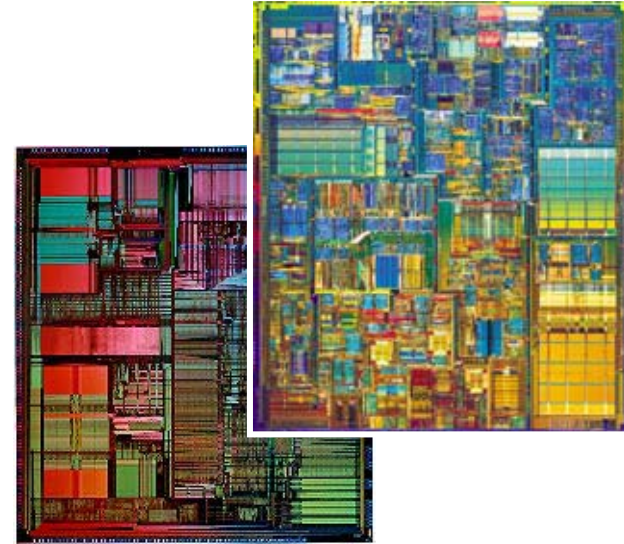
1978

More Recently

Ultra **L**arge **S**cale **I**ntegration

System on **C**hip (**SoC**)

20 ~ 30 million transistors in 2002



The chip complexity has increased by a factor of 1000 since its first introduction, but the term **VLSI** remained virtually universal to denote digital integrated systems with high complexity.

Some Leading-Edge Examples



Intel Pentium 4

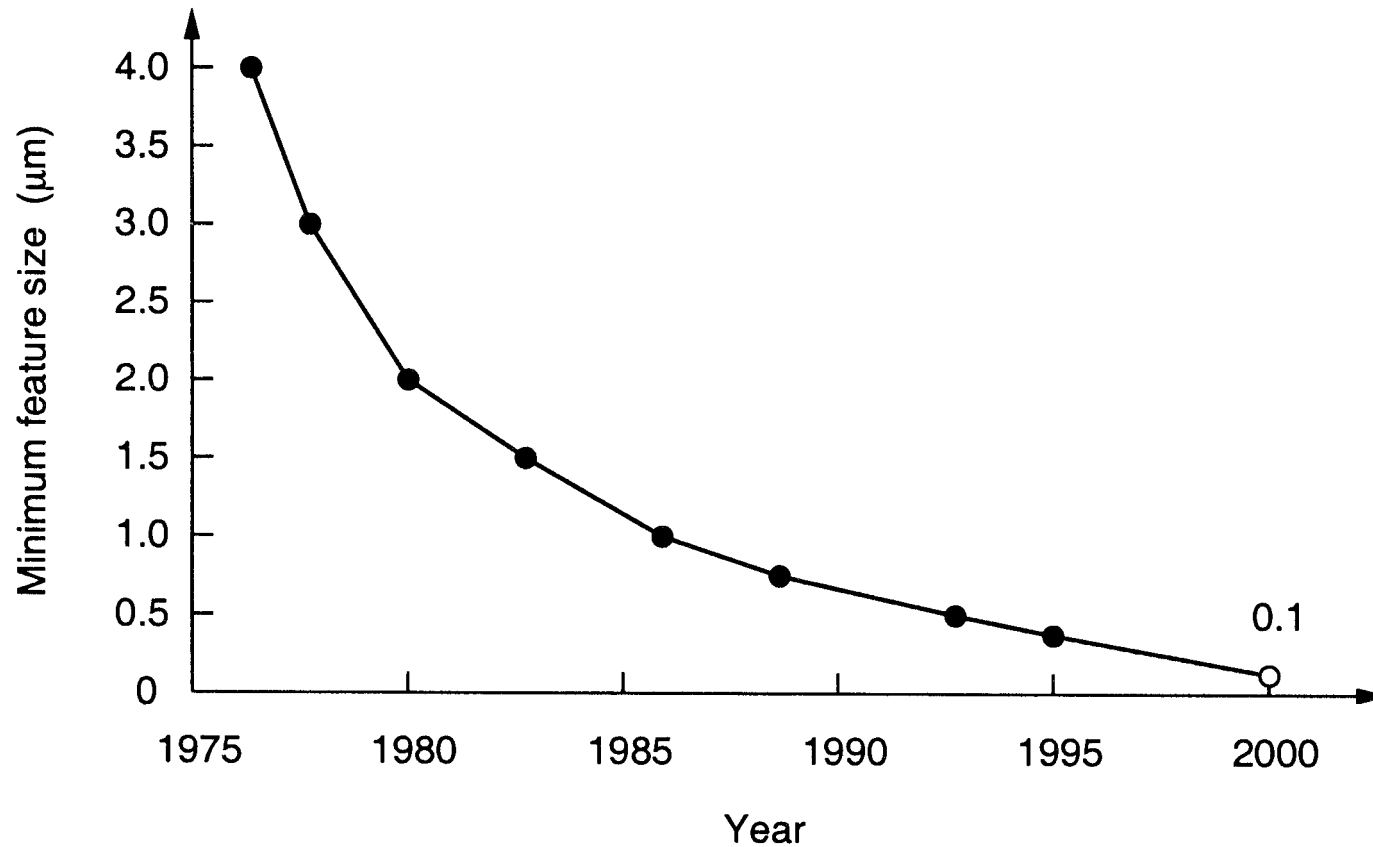
0.13 μ process

55 million transistors

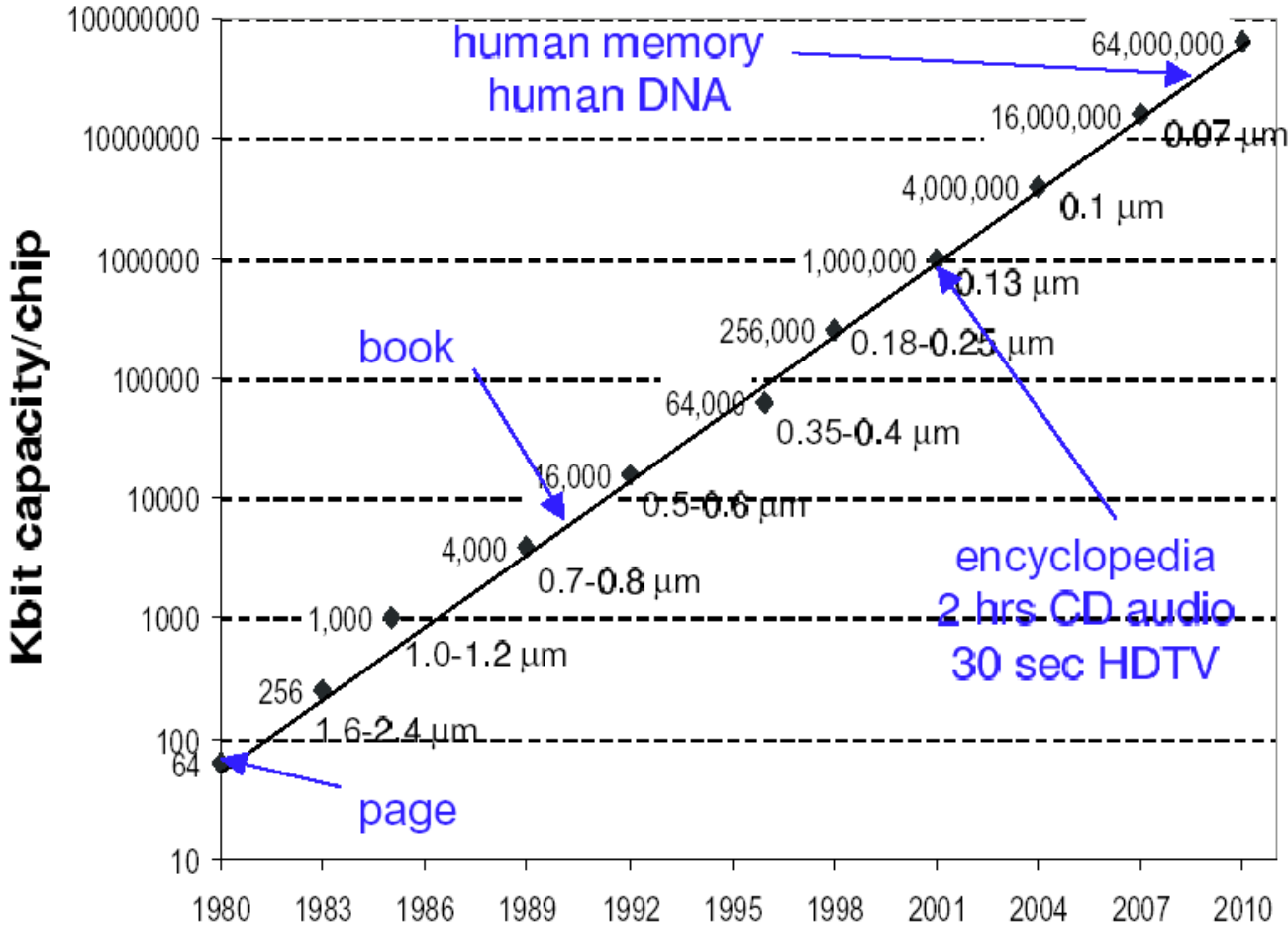
2.4GHz clock

145mm²

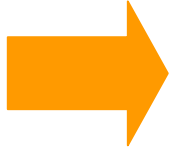
Evolution of Minimum Feature Size



Evolution of Memory Capacity

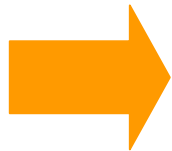


Shrinking Device Dimensions



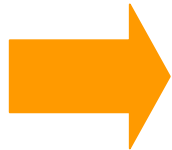
| YEAR | 2002 | 2005 | 2008 | 2011 | 2014 |
|-------------------------------|---------------------|---------------------|---------------------|---------------------|---------------------|
| TECHNOLOGY | 130 nm | 100 nm | 70 nm | 50 nm | 35 nm |
| CHIP SIZE | 400 mm ² | 600 mm ² | 750 mm ² | 800 mm ² | 900 mm ² |
| NUMBER OF TRANSISTORS (LOGIC) | 400 M | 1 Billion | 3 Billion | 6 Billion | 16 Billion |
| DRAM CAPACITY | 2 Gbits | 10 Gbits | 25 Gbits | 70 Gbits | 200 Gbits |
| MAXIMUM CLOCK FREQUENCY | 1.6 GHz | 2.0 GHz | 2.5 GHz | 3.0 GHz | 3.5 GHz |
| MINIMUM SUPPLY VOLTAGE | 1.5 V | 1.2 V | 0.9 V | 0.6 V | 0.6 V |
| MAXIMUM POWER DISSIPATION | 130 W | 160 W | 170 W | 175 W | 180 W |
| MAXIMUM NUMBER OF I/O PINS | 2500 | 4000 | 4500 | 5500 | 6000 |

Increasing Function Density



| YEAR | 2002 | 2005 | 2008 | 2011 | 2014 |
|--------------------------------------|---------------------|---------------------|---------------------|---------------------|---------------------|
| TECHNOLOGY | 130 nm | 100 nm | 70 nm | 50 nm | 35 nm |
| CHIP SIZE | 400 mm ² | 600 mm ² | 750 mm ² | 800 mm ² | 900 mm ² |
| NUMBER OF TRANSISTORS (LOGIC) | 400 M | 1 Billion | 3 Billion | 6 Billion | 16 Billion |
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| MAXIMUM POWER DISSIPATION | 130 W | 160 W | 170 W | 175 W | 180 W |
| MAXIMUM NUMBER OF I/O PINS | 2500 | 4000 | 4500 | 5500 | 6000 |

Increasing Clock Frequency

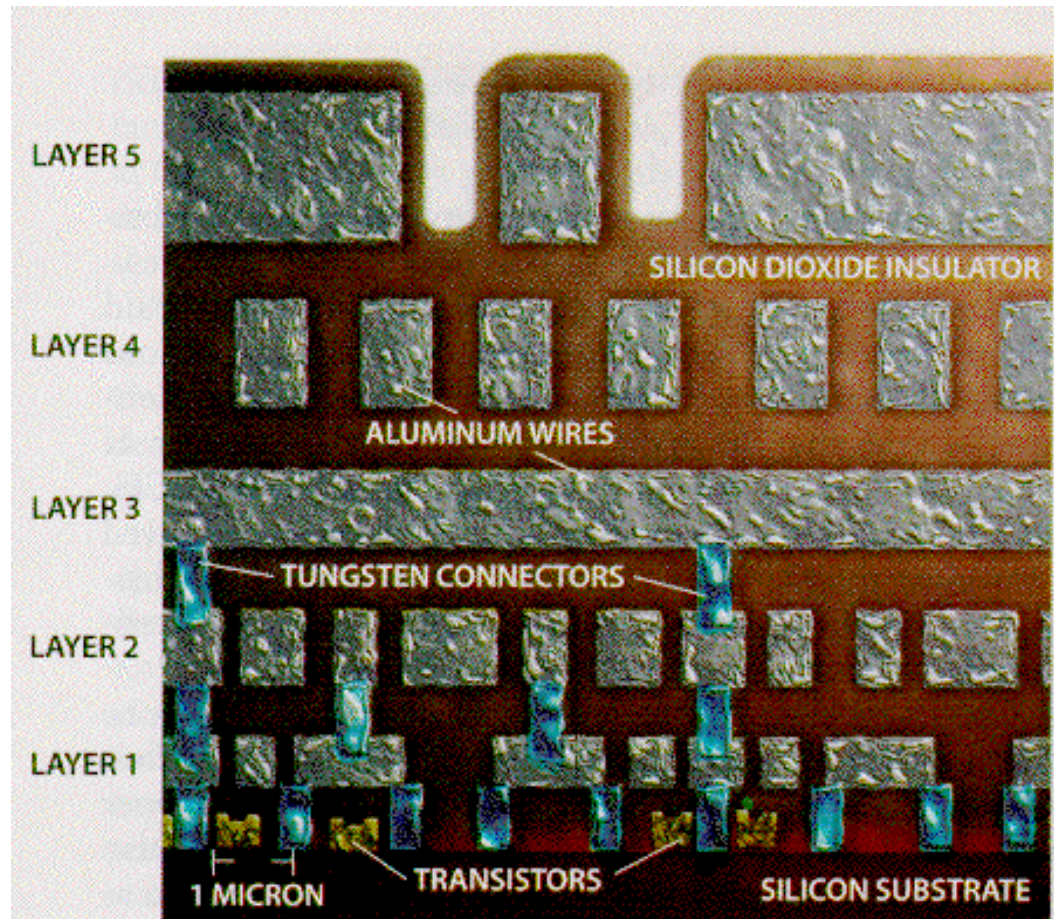


| YEAR | 2002 | 2005 | 2008 | 2011 | 2014 |
|--------------------------------|---------------------|---------------------|---------------------|---------------------|---------------------|
| TECHNOLOGY | 130 nm | 100 nm | 70 nm | 50 nm | 35 nm |
| CHIP SIZE | 400 mm ² | 600 mm ² | 750 mm ² | 800 mm ² | 900 mm ² |
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| MAXIMUM POWER DISSIPATION | 130 W | 160 W | 170 W | 175 W | 180 W |
| MAXIMUM NUMBER OF I/O PINS | 2500 | 4000 | 4500 | 5500 | 6000 |

Decreasing Supply Voltage

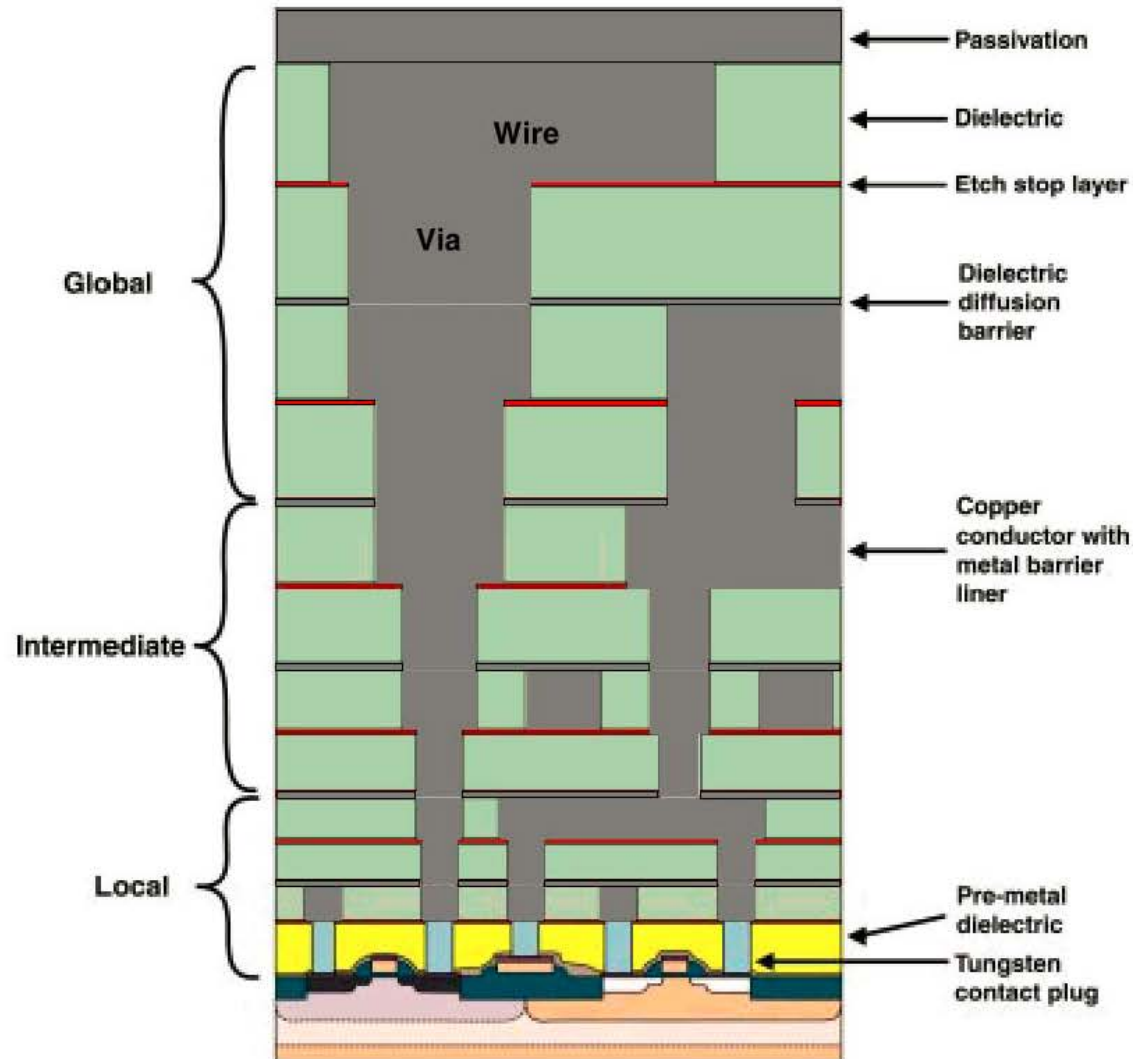
| YEAR | 2002 | 2005 | 2008 | 2011 | 2014 |
|----------------------------------|---------------------|---------------------|---------------------|---------------------|---------------------|
| TECHNOLOGY | 130 nm | 100 nm | 70 nm | 50 nm | 35 nm |
| CHIP SIZE | 400 mm ² | 600 mm ² | 750 mm ² | 800 mm ² | 900 mm ² |
| NUMBER OF TRANSISTORS (LOGIC) | 400 M | 1 Billion | 3 Billion | 6 Billion | 16 Billion |
| DRAM CAPACITY | 2 Gbits | 10 Gbits | 25 Gbits | 70 Gbits | 200 Gbits |
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| MINIMUM SUPPLY VOLTAGE | 1.5 V | 1.2 V | 0.9 V | 0.6 V | 0.6 V |
| MAXIMUM POWER DISSIPATION | 130 W | 160 W | 170 W | 175 W | 180 W |
| MAXIMUM NUMBER OF I/O PINS | 2500 | 4000 | 4500 | 5500 | 6000 |





5-layer cross-section of chip

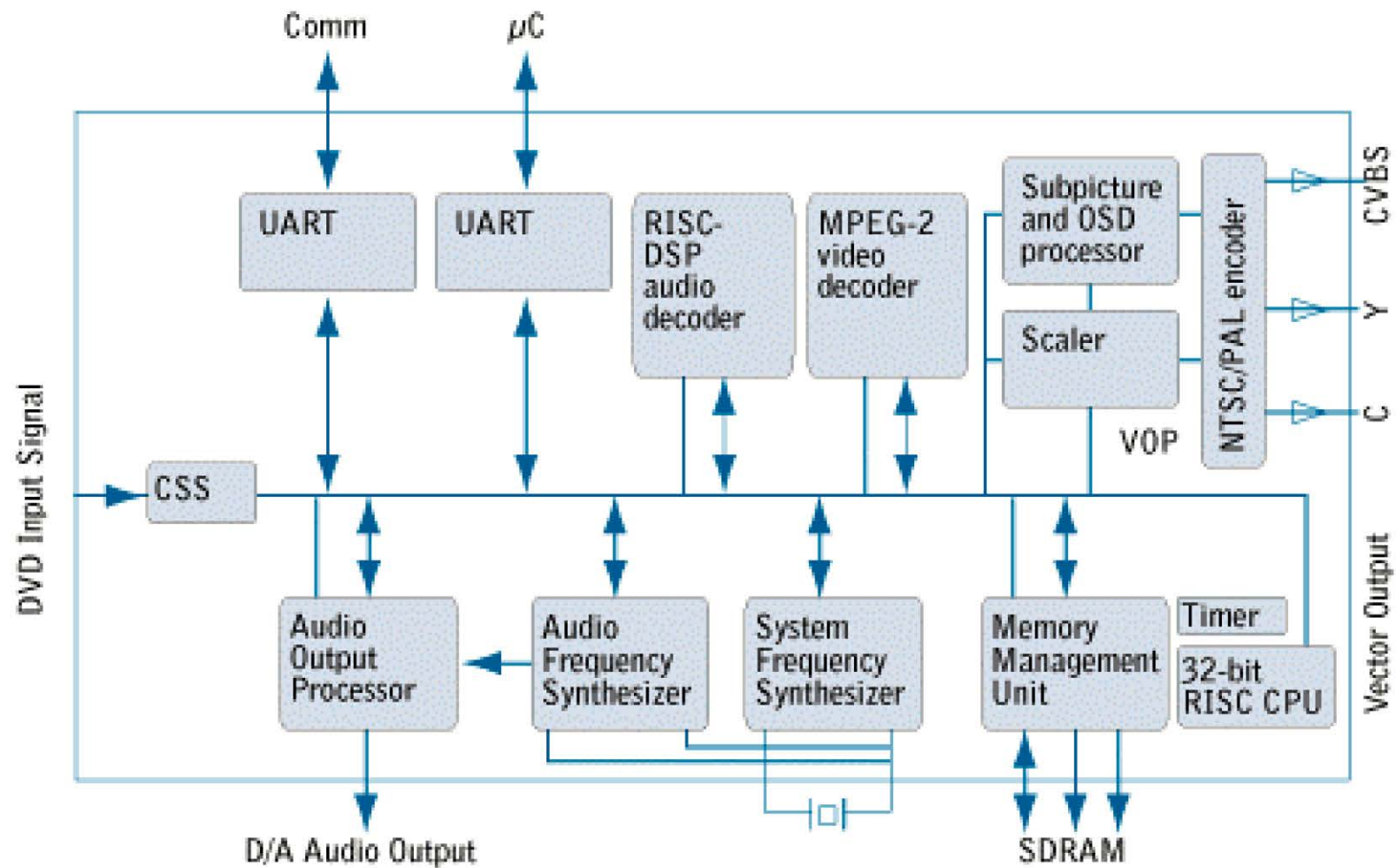
Typical Chip Cross Section



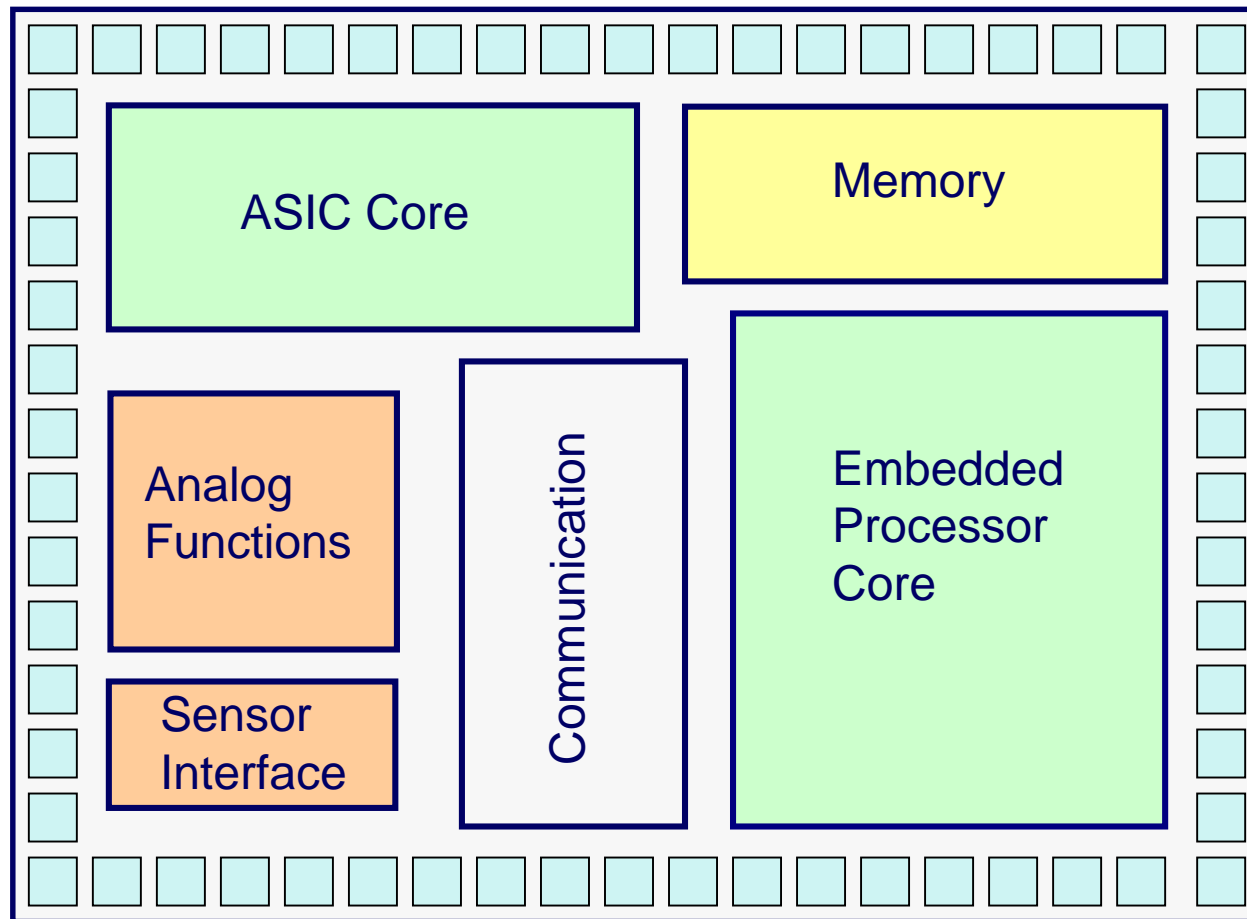
System-on-Chip

Integrating all or most of the components of a hybrid system on a single substrate (silicon or MCM), rather than building a conventional printed circuit board.

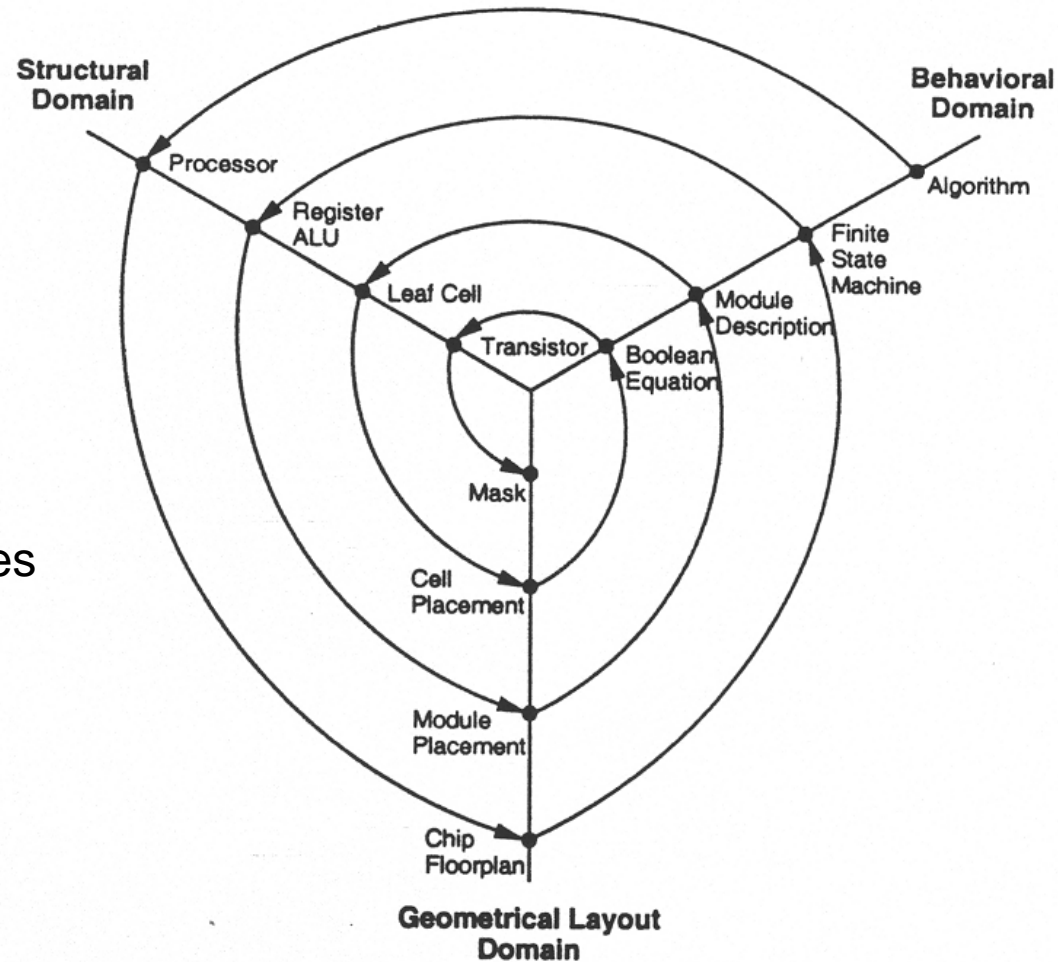
1. More compact system realization
2. Higher speed / performance
 - Better reliability
 - Less expensive !



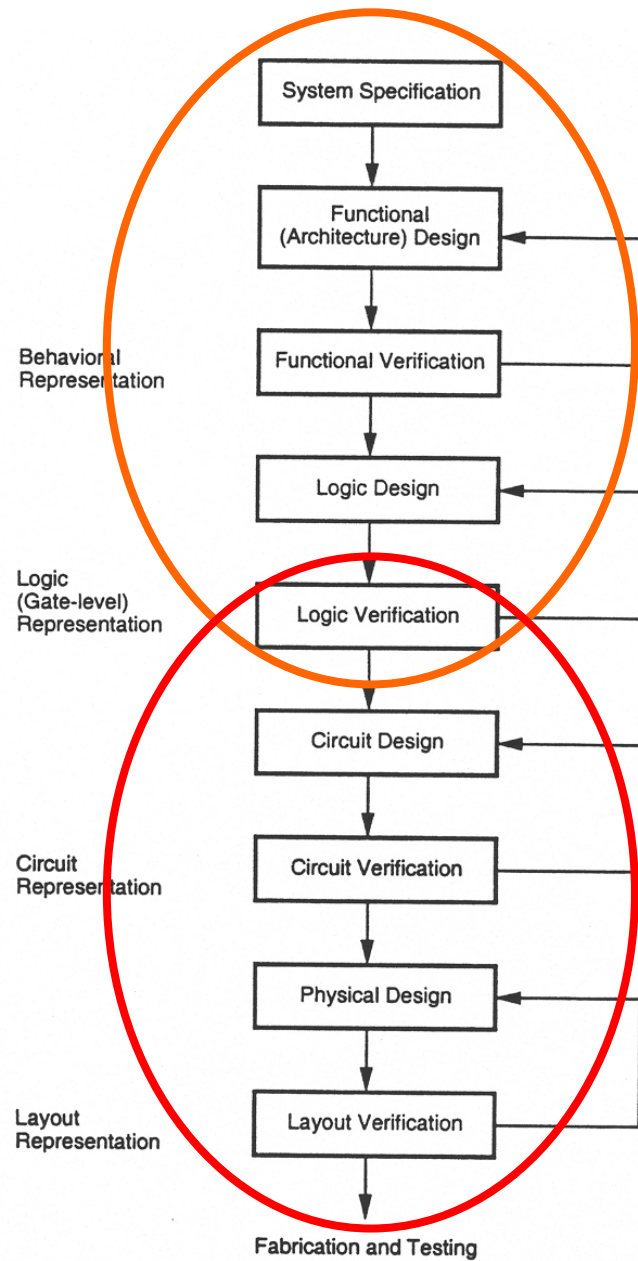
New Direction: System-on-Chip (SoC)



The Y-Chart



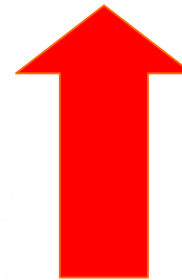
Notice: There is a need for structured design methodologies to handle the high level of complexity !



Simplified VLSI Design Flow



Top-down

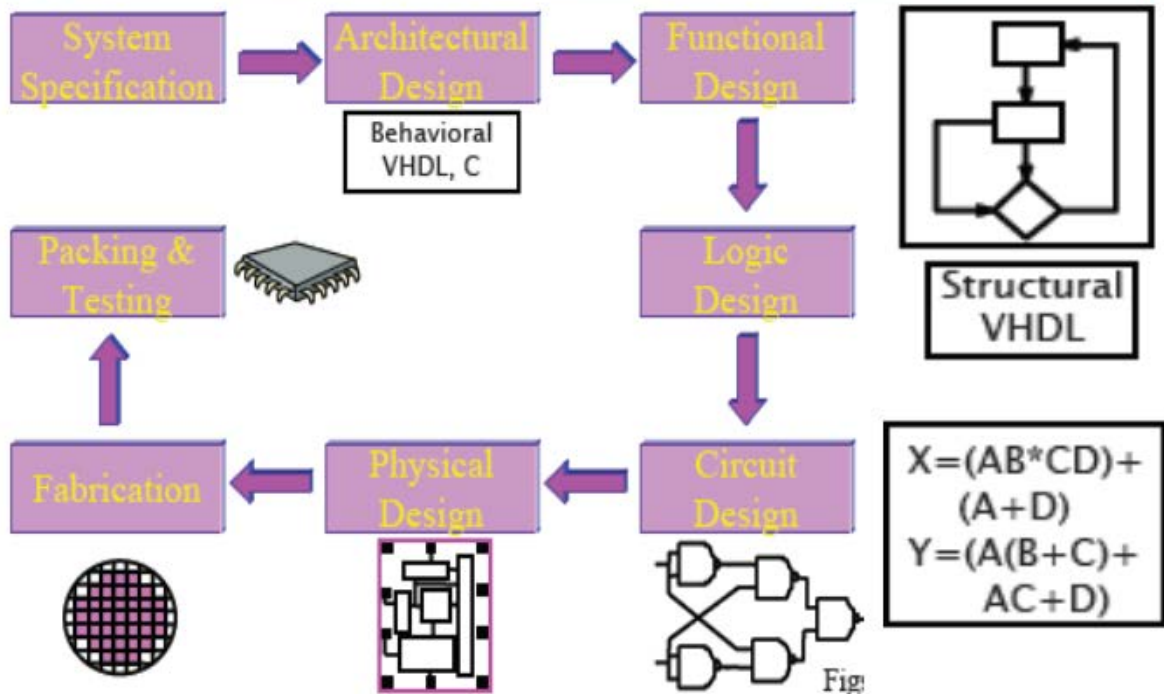


Bottom-up

Top-down vs. bottom-up design

- **Top-down design adds functional detail.**
 - **Create lower levels of abstraction from upper levels.**
- **Bottom-up design creates abstractions from low-level behavior.**
- **Good design needs both top-down and bottom-up efforts.**

VLSI Design Cycle



VLSI Design Cycle

- **System Specification**

- A high level representation of the system

- Considered factors

- » Performance

- » Functionality

- » Physical dimensions (die size)



- Result Specs – size, speed, power, and functionality

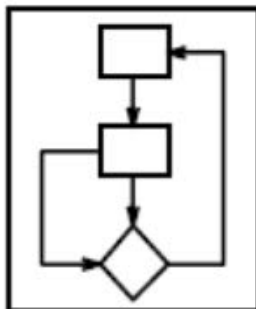
VLSI Design Cycle

- **Architectural Design**
 - RISC (Reduced Instruction Set Computer) versus CISC (Complex Instruction Set Computer)
 - Number of ALUs, Floating Point Units
 - Number and structure of pipelines
 - Cache size
 - Prediction on die size, power, and speed based on existing design
 - Early estimation are very important here

VLSI Design Cycle

Behavioral or Functional Design

- Only behavior and timing without implementation issue
- Specify behavior based on Input + output + timing
- Fast emulation and debugging for the system



```
always @(posedge clk);
begin
  if (enable_ == 1'b0)
    data = 0;
  else
    data = data + 1;
end
```

HDL-Based Design

1980's

Hardware Description Languages (HDL) were conceived to facilitate the information exchange between design groups.

1990's

The increasing computation power led to the introduction of logic synthesizers that can translate the description in HDL into a synthesized gate-level net-list of the design.

2000's

Modern synthesis algorithms can optimize a digital design and explore different alternatives to identify the design that best meets the requirements.

VLSI Design Cycle

- **Logic Design**

- Control flow, word widths, register allocation, arithmetic operations, and logic operations
- RTL (Register Transfer Level) – HDL (Hardware Description Language)
 - » Verilog – most popular
 - » VHDL – Europe and Eastern
 - » Literal + Timing Information

$$\begin{aligned} X &= (AB * CD) + \\ &\quad (A + D) \\ Y &= (A(B + C) + \\ &\quad AC + D) \end{aligned}$$

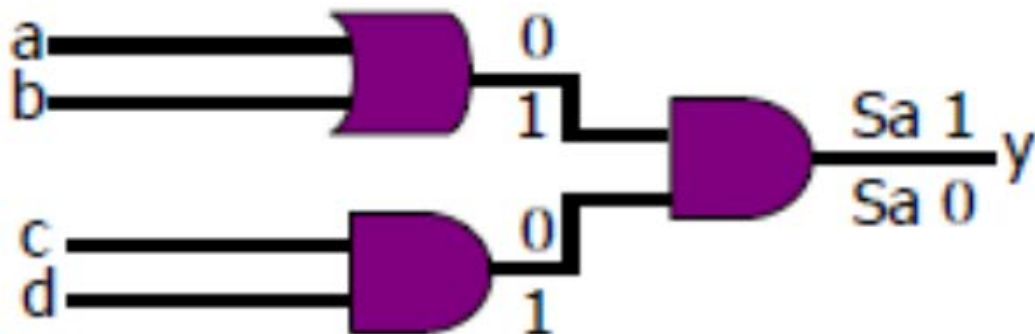


Boolean Expression
Timing Information

VLSI Design Cycle

■ Logic Design

- More actual simulation and testing

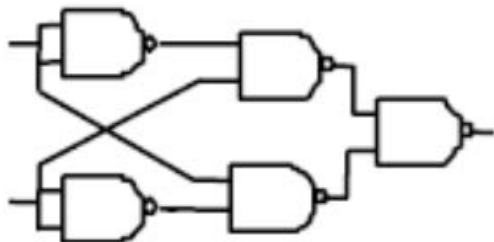


- High Level Synthesis: Produce a RTL description from a behavioral description of the design

VLSI Design Cycle

Circuit Design

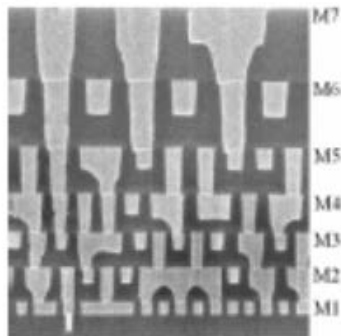
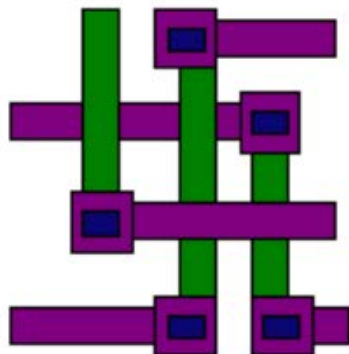
- Boolean Expression → Circuit Elements (Cells, Macros, Gates, Transistors) + Interconnection
- Each component has specific timing and power Info.
- Circuit Simulation : Verify the correctness and timing
- Terms – Netlist, Schematic
- Logic Synthesis Tools : RTL → Netlist



VLSI Design Cycle

Physical Design

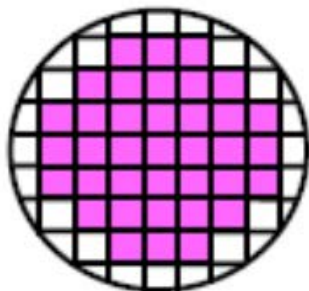
- Netlist → Layout (Geometry Representation)
 - » Design rules of applied fabrication process
- Layout Synthesis Tools
 - » Automatic conversion (Fully/Partially)
 - » Area and performance penalty
- Crucial Challenges – Area/Delay



VLSI Design Cycle

Fabrication

- Layout → Photo-lithographic mask
 - » One mask for each layer
- Wafer : Silicon crystal are grown & sliced
- Deposition, and diffusion of various materials on the wafer : each step uses one mask
- Term : Tape Out, 8 inch/20cm, 12 inch/30cm



VLSI Design Cycle

Packaging, Testing, and Debugging

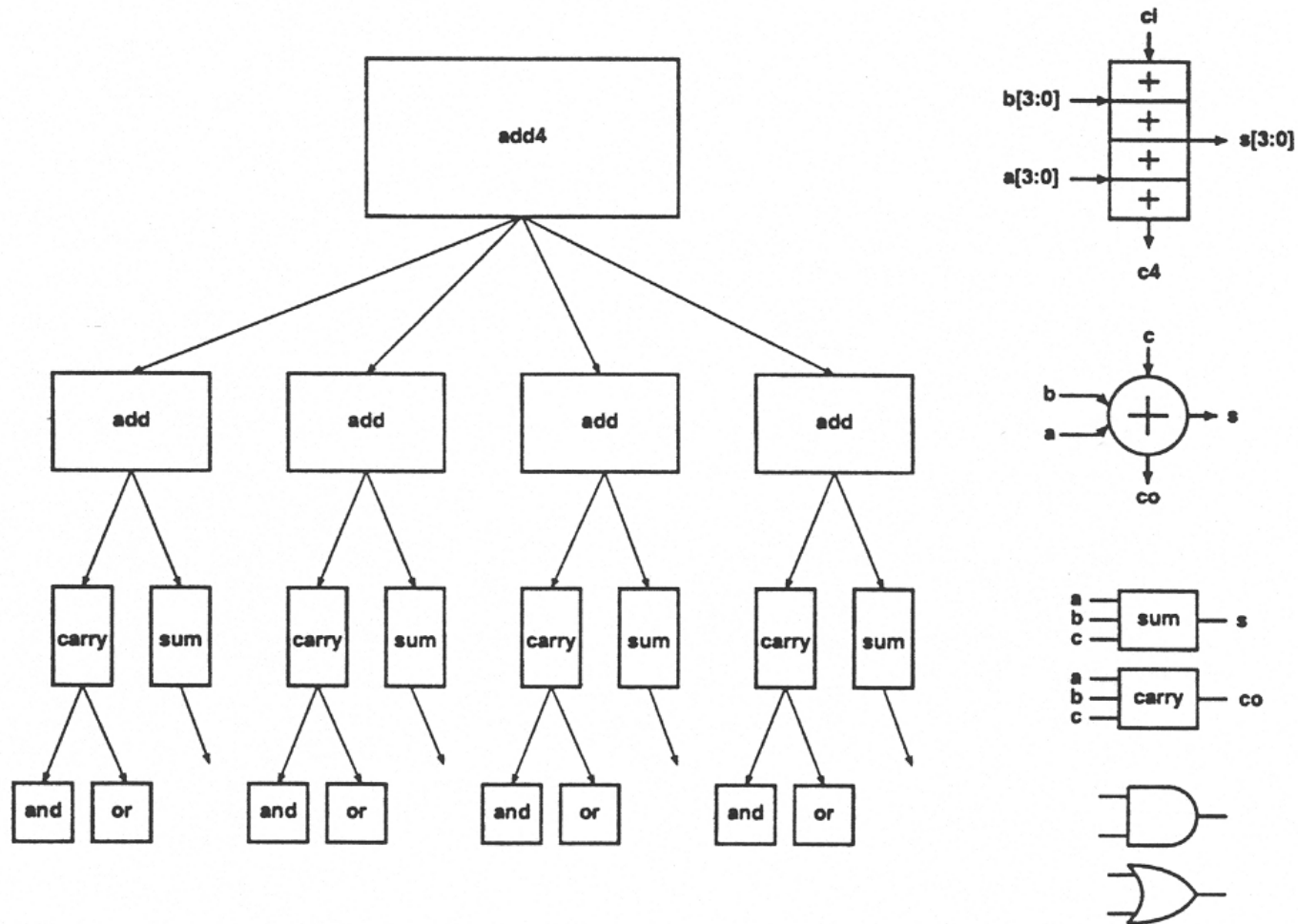
- For PCB (Printed Circuit Board) : DIP (Dual In-line Package), PGA (Pin Grid Array), BGA (Ball Grid Array), and QFP (Quad Flat Package)
- For MCM (Multi-Chip Modules): no packaged
- Testing
 - » Before Package – Probe line testing
 - » After Package – Tester machine applies test patterns.



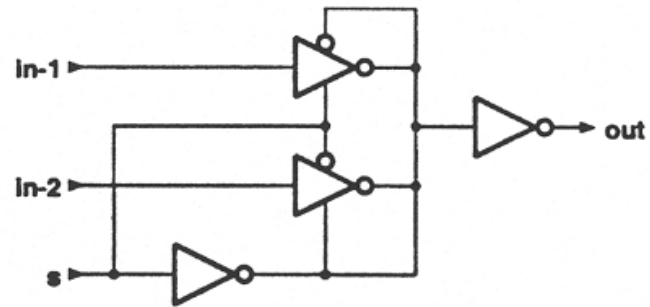
Structured Design Principles

- Hierarchy:** “Divide and conquer” technique involves dividing a module into sub-modules and then repeating this operation on the sub-modules until the complexity of the smaller parts becomes manageable.
- Regularity:** The hierarchical decomposition of a large system should result in not only **simple**, but also **similar** blocks, as much as possible. Regularity usually reduces the number of different modules that need to be designed and verified, at all levels of abstraction.
- Modularity:** The various functional blocks which make up the larger system must have **well-defined functions** and **interfaces**.
- Locality:** Internal details remain at the local level. The concept of locality also ensures that connections are mostly between neighboring modules, **avoiding long-distance connections** as much as possible.

Hierarchy of a 4-bit Carry Ripple Adder



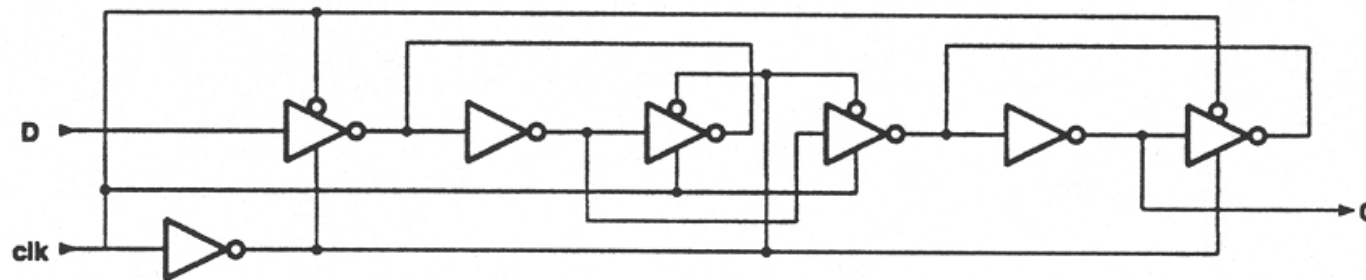
Regularity



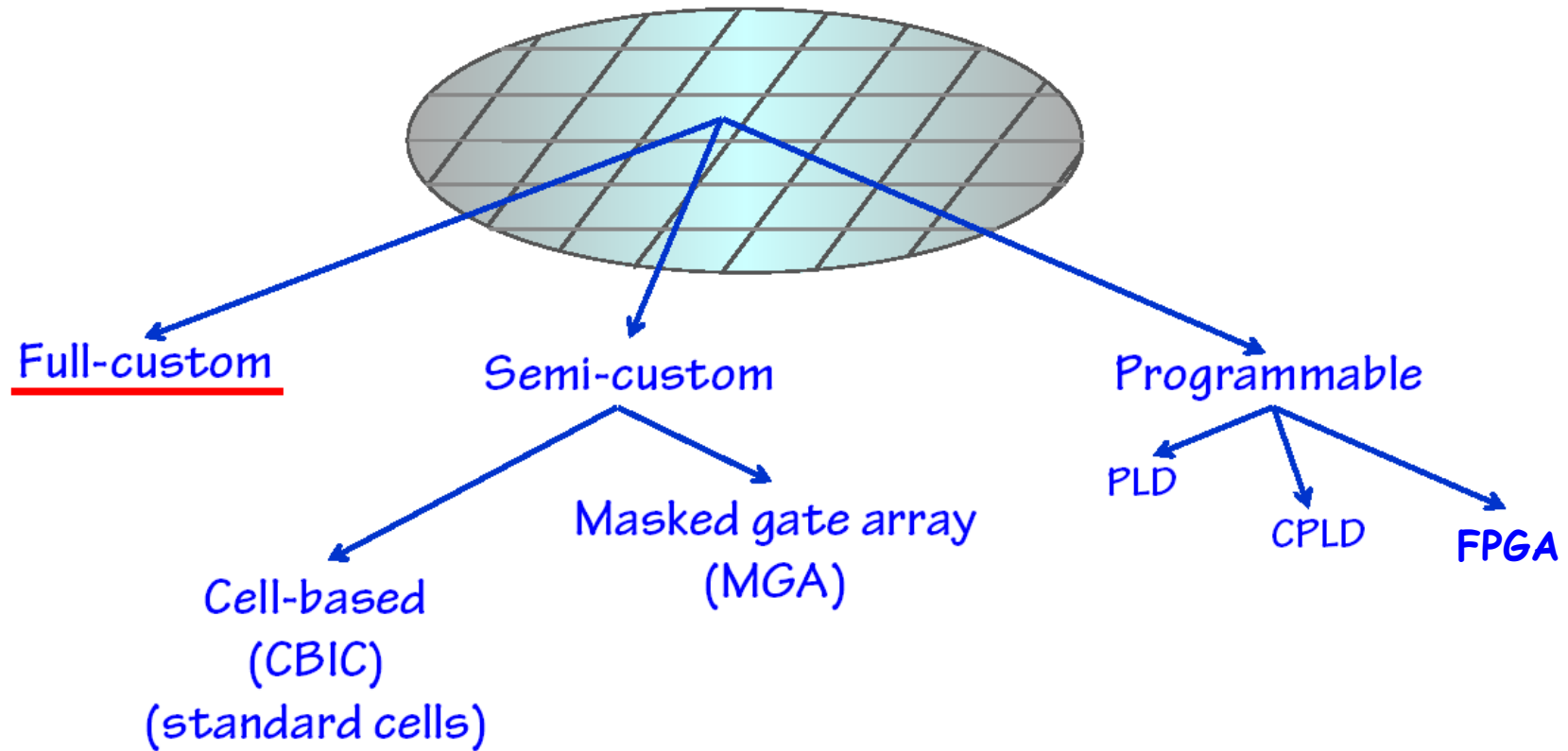
2-input MUX

(a)

DFF

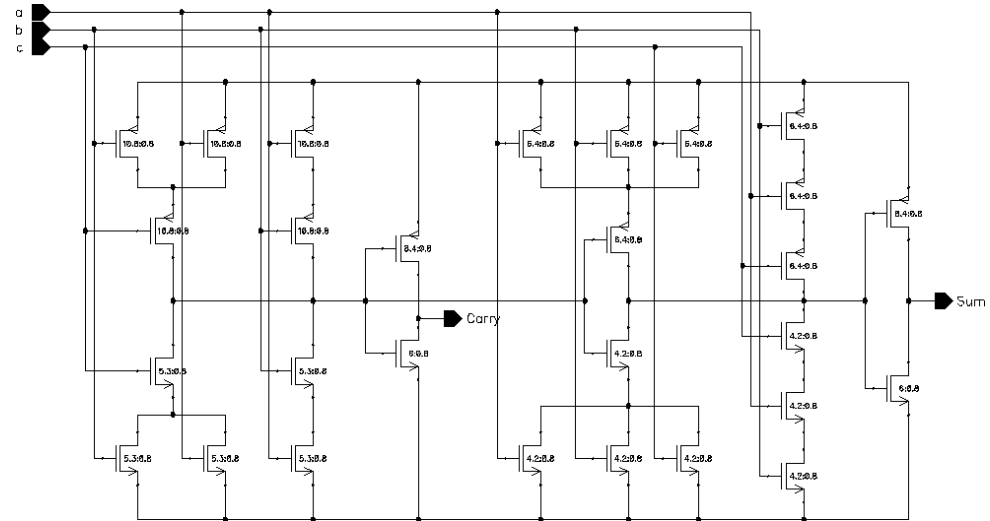


VLSI Design Styles

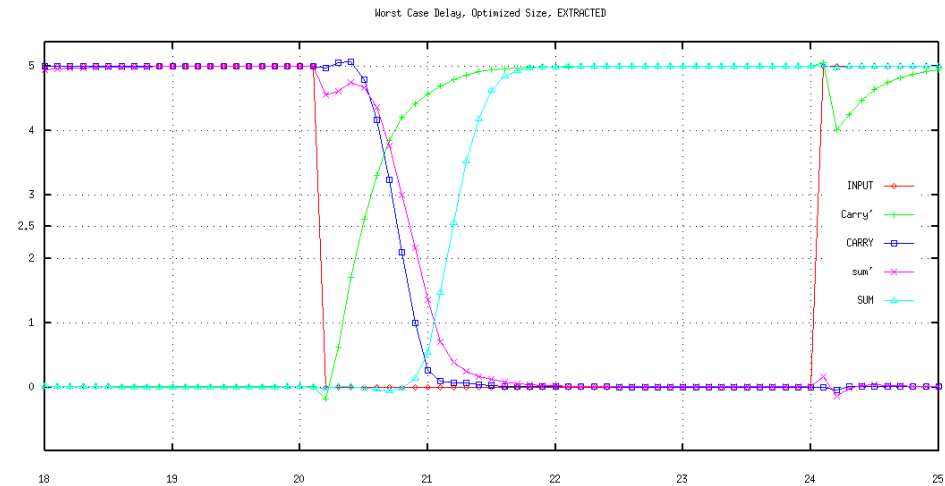


Full Custom Design

Following the partitioning, the transistor level design of the building block is generated and simulated.

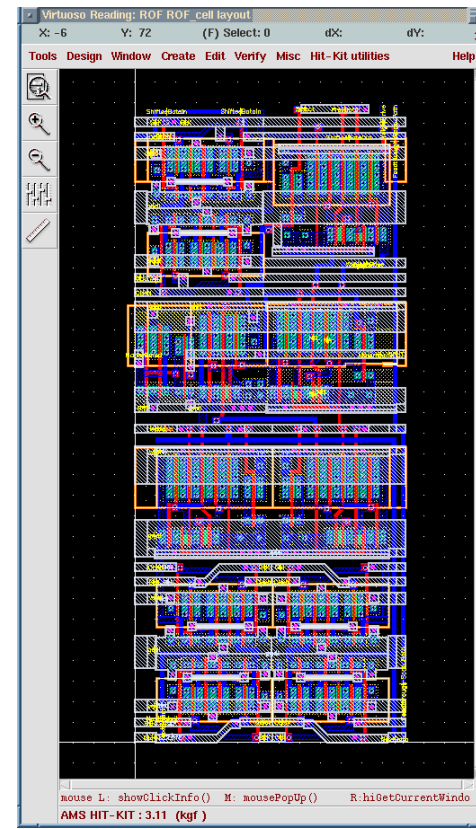
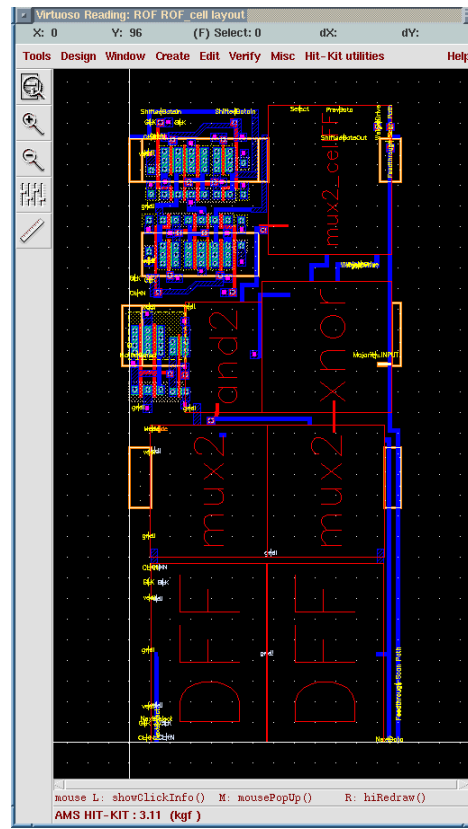
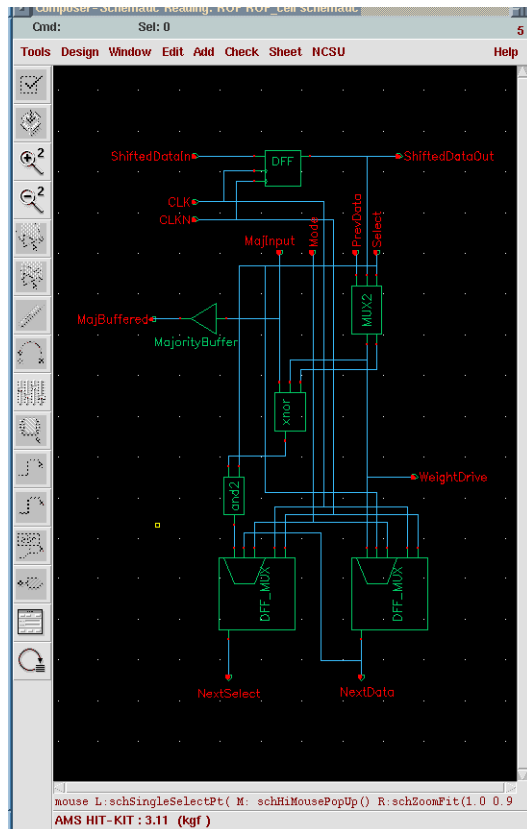


The example shows a 1-bit full-adder schematic and its SPICE simulation results.

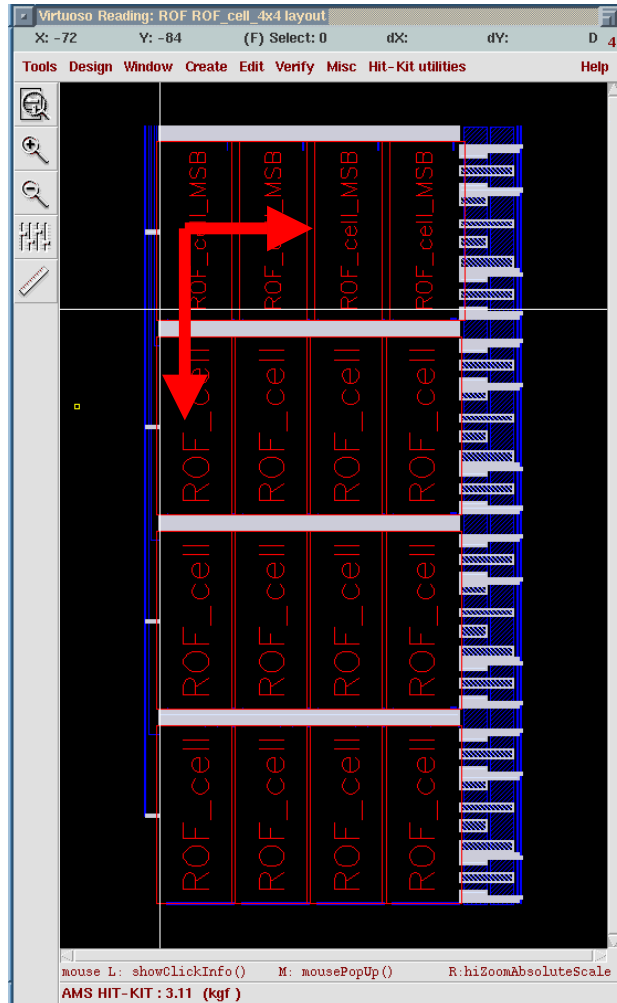


Full Custom Design

The main objective of full custom design is to ensure fine-grained regularity and modularity.



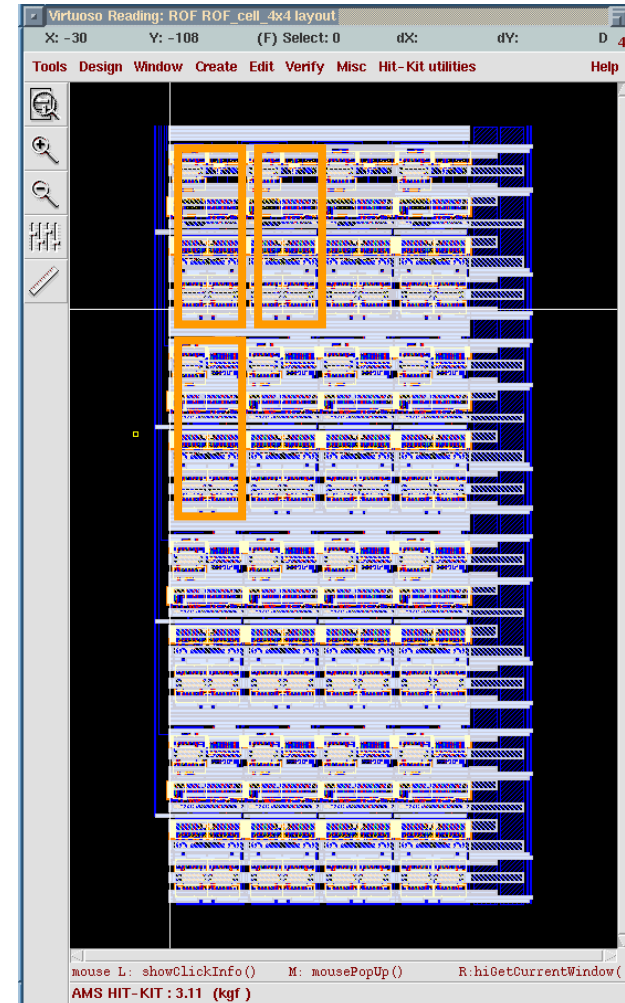
Full Custom Design



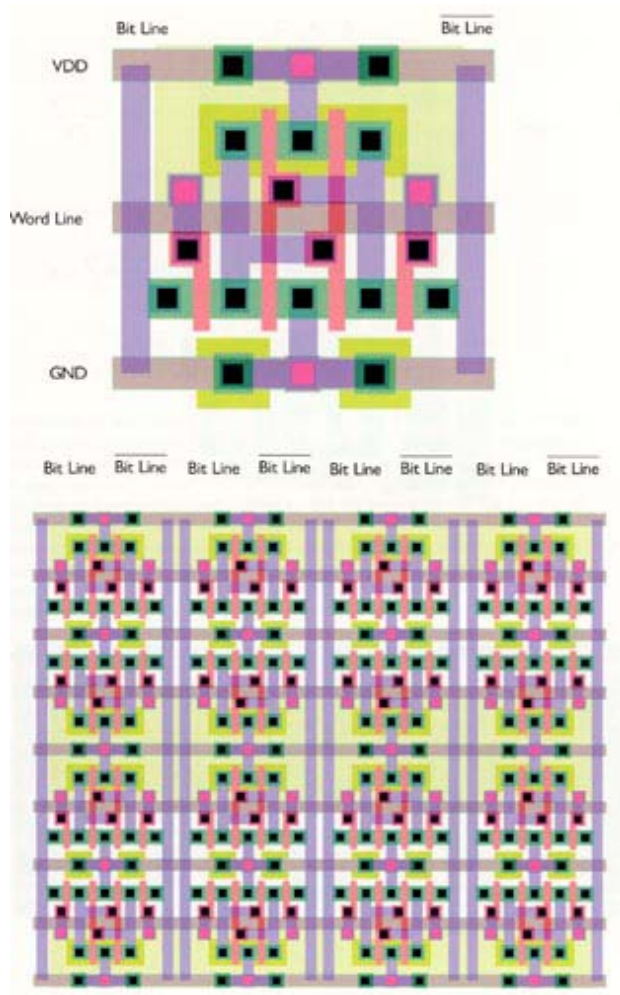
A carefully crafted full custom block can be placed both along the X and Y axis to form an interconnected two-dimensional array.

Example:

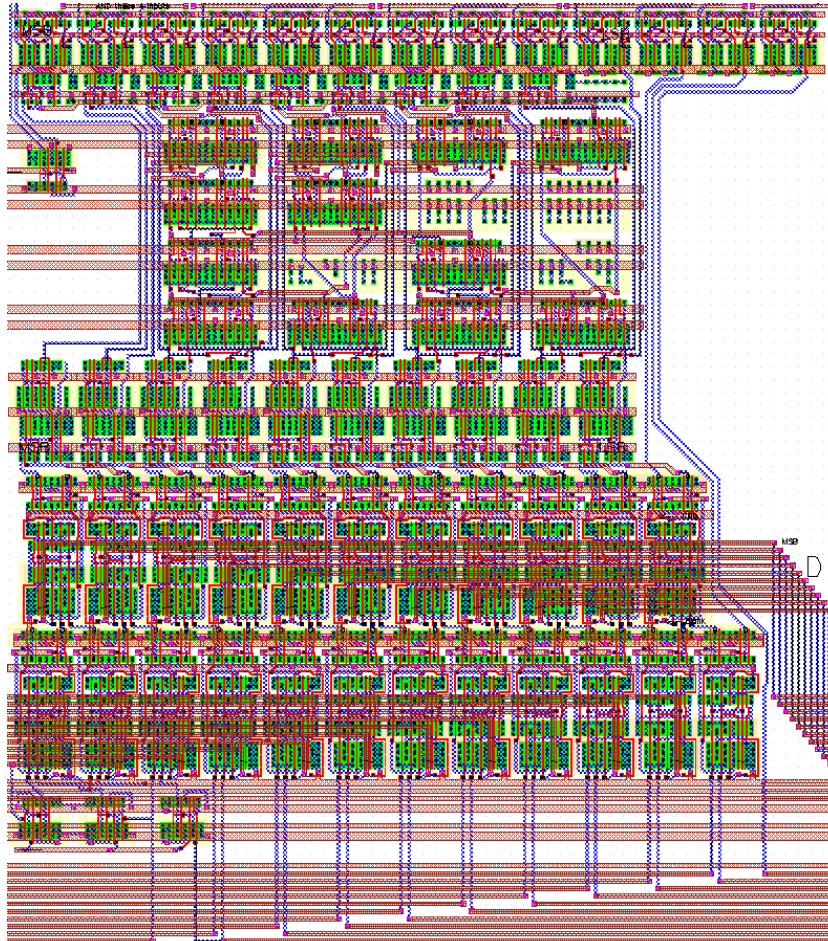
Data-path cells



Full Custom SRAM Cell Design

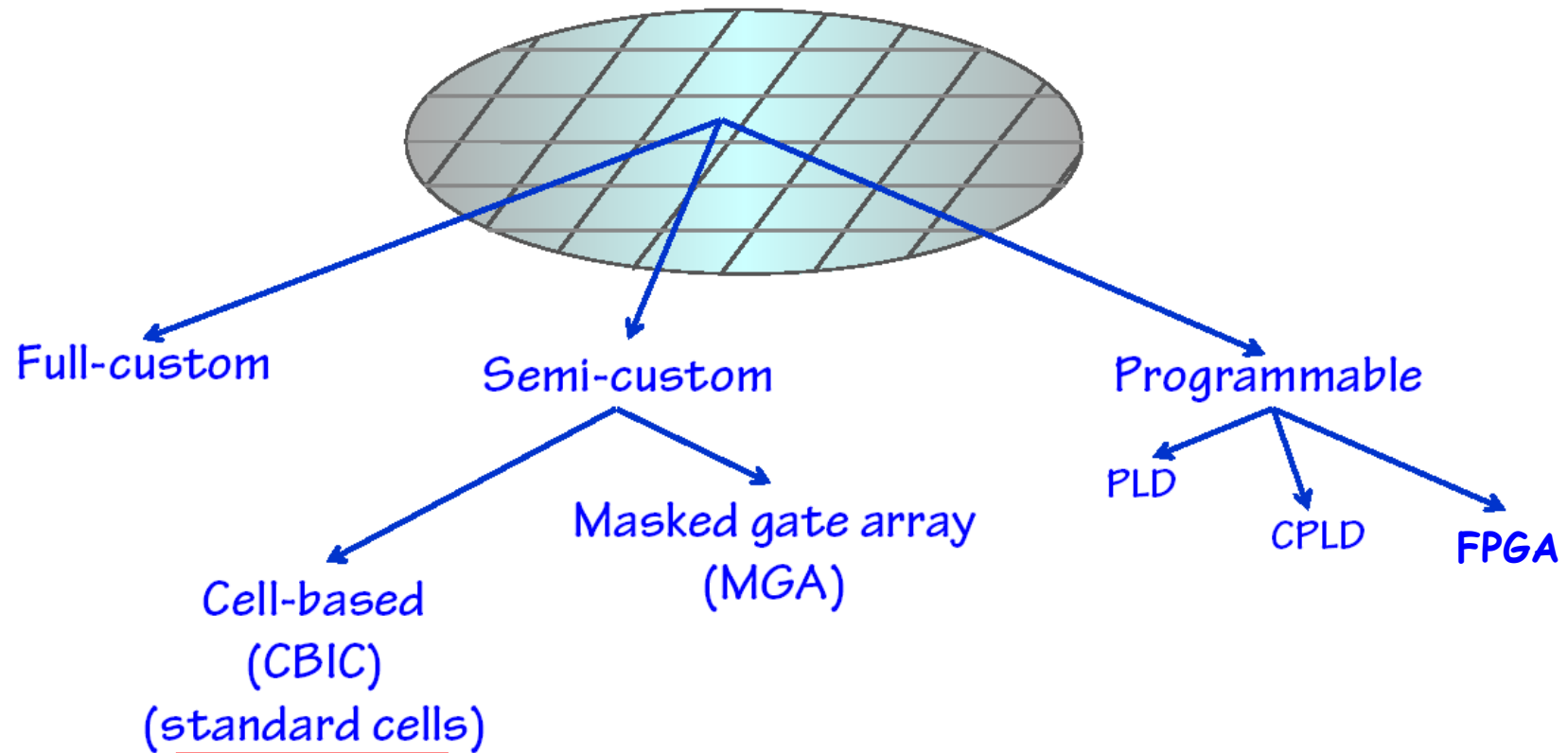


Mapping the Design into Layout

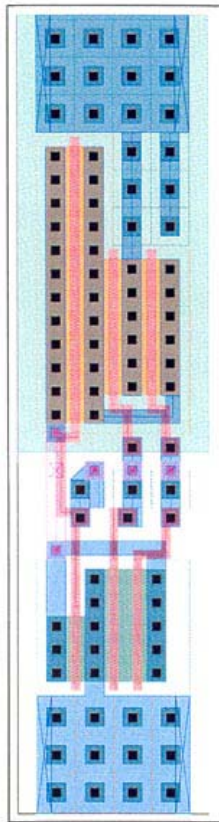


Manual full-custom design can be very challenging and time consuming, especially if the low level regularity is not well defined !

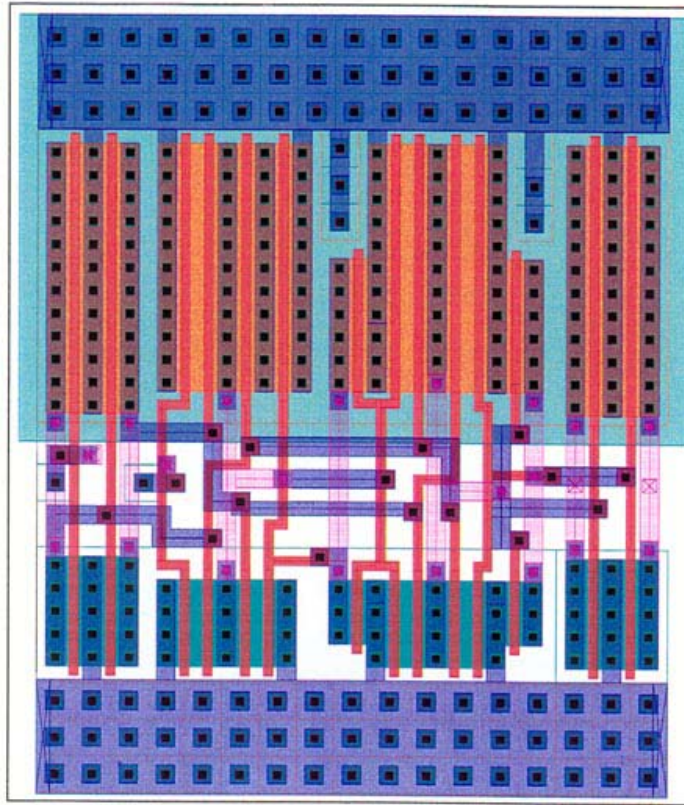
VLSI Design Styles



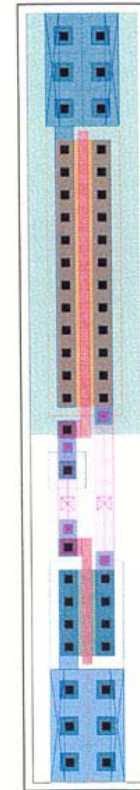
Standard Cells



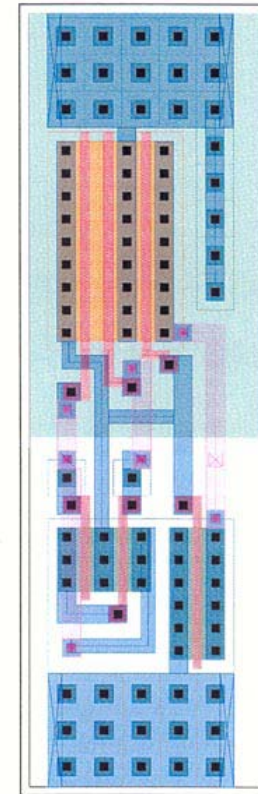
AND



DFF

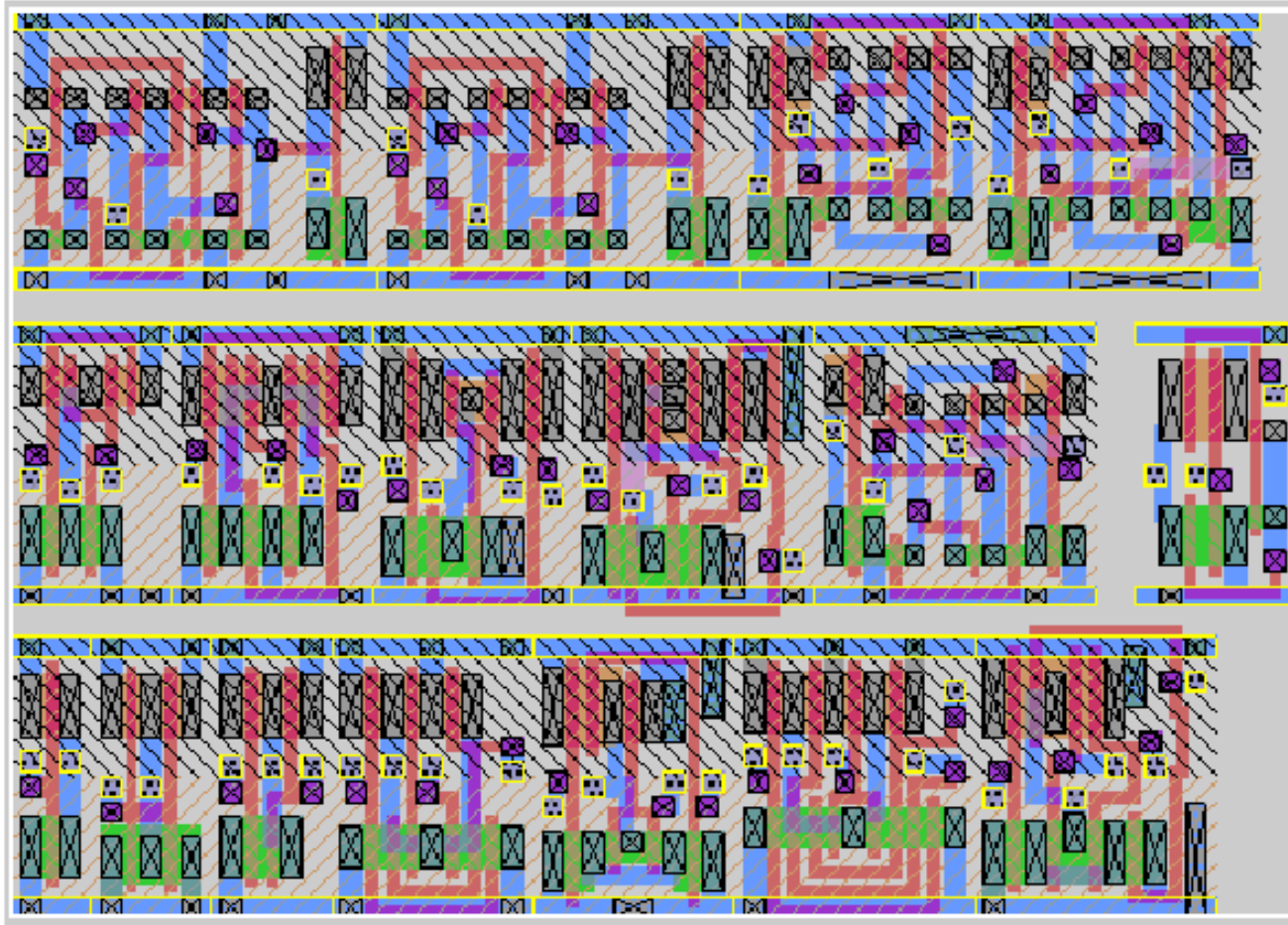


INV

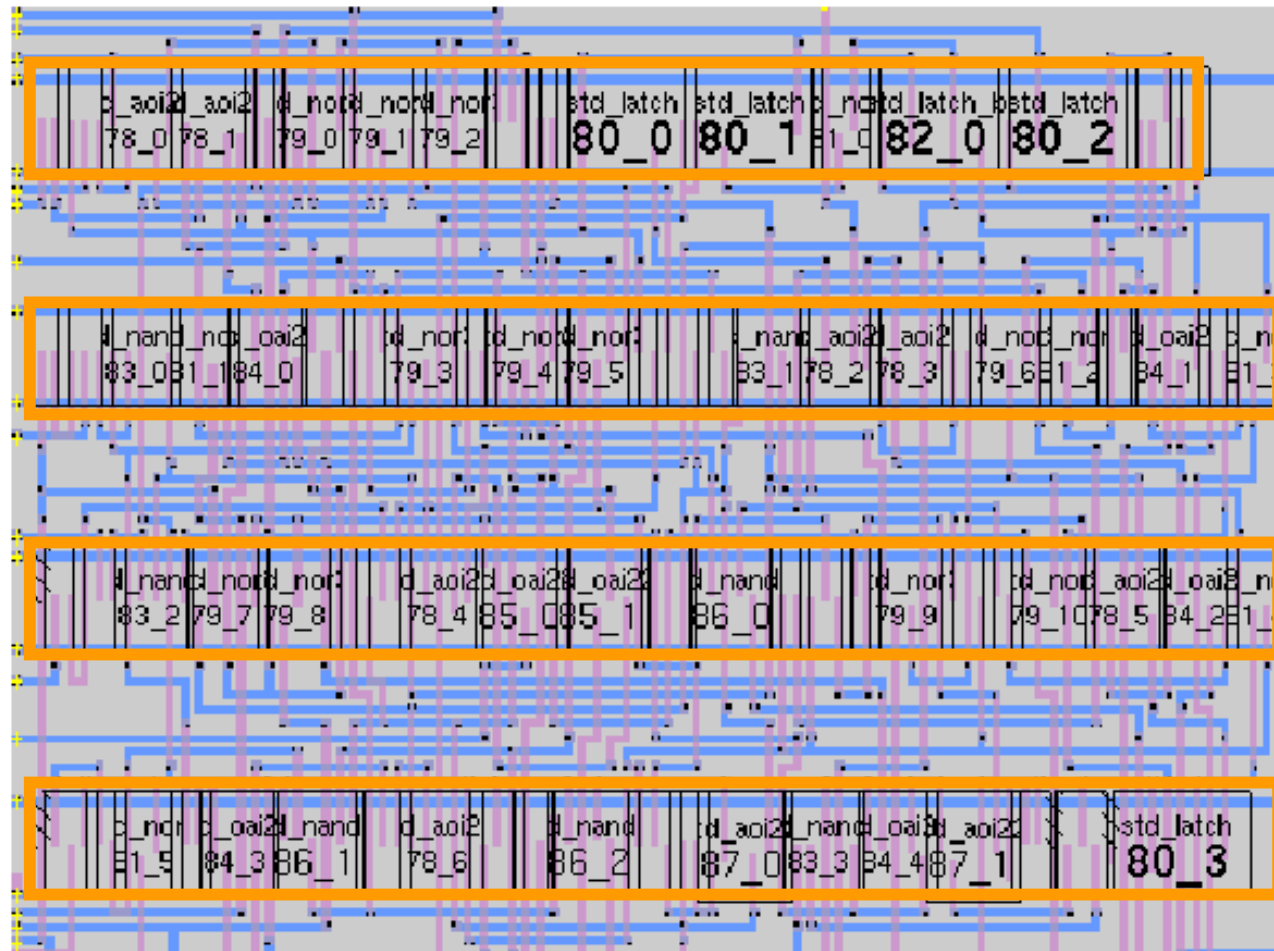


XOR

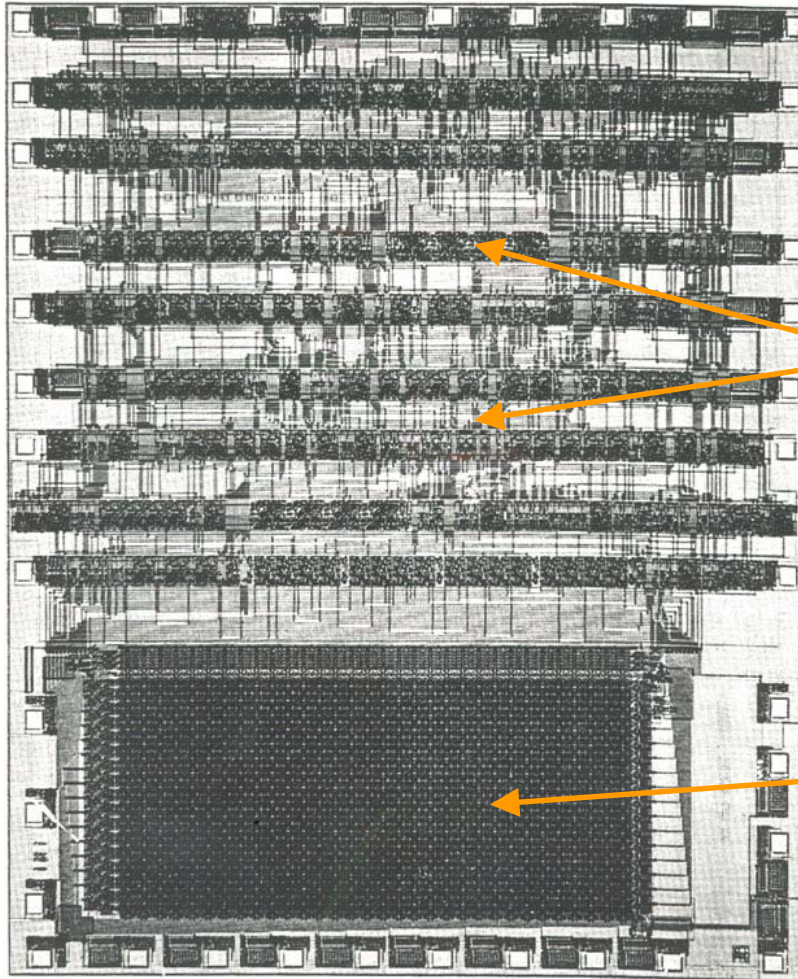
Standard Cells



Standard Cells



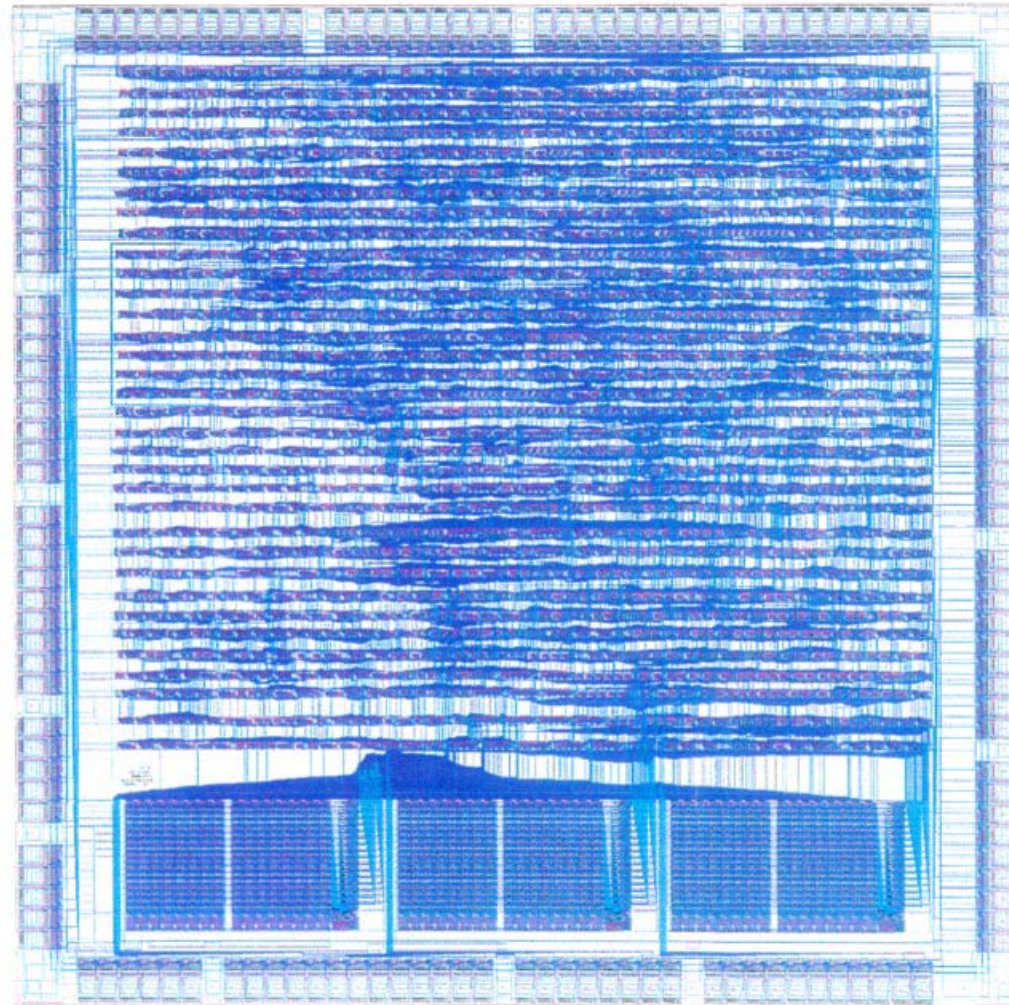
Standard Cells



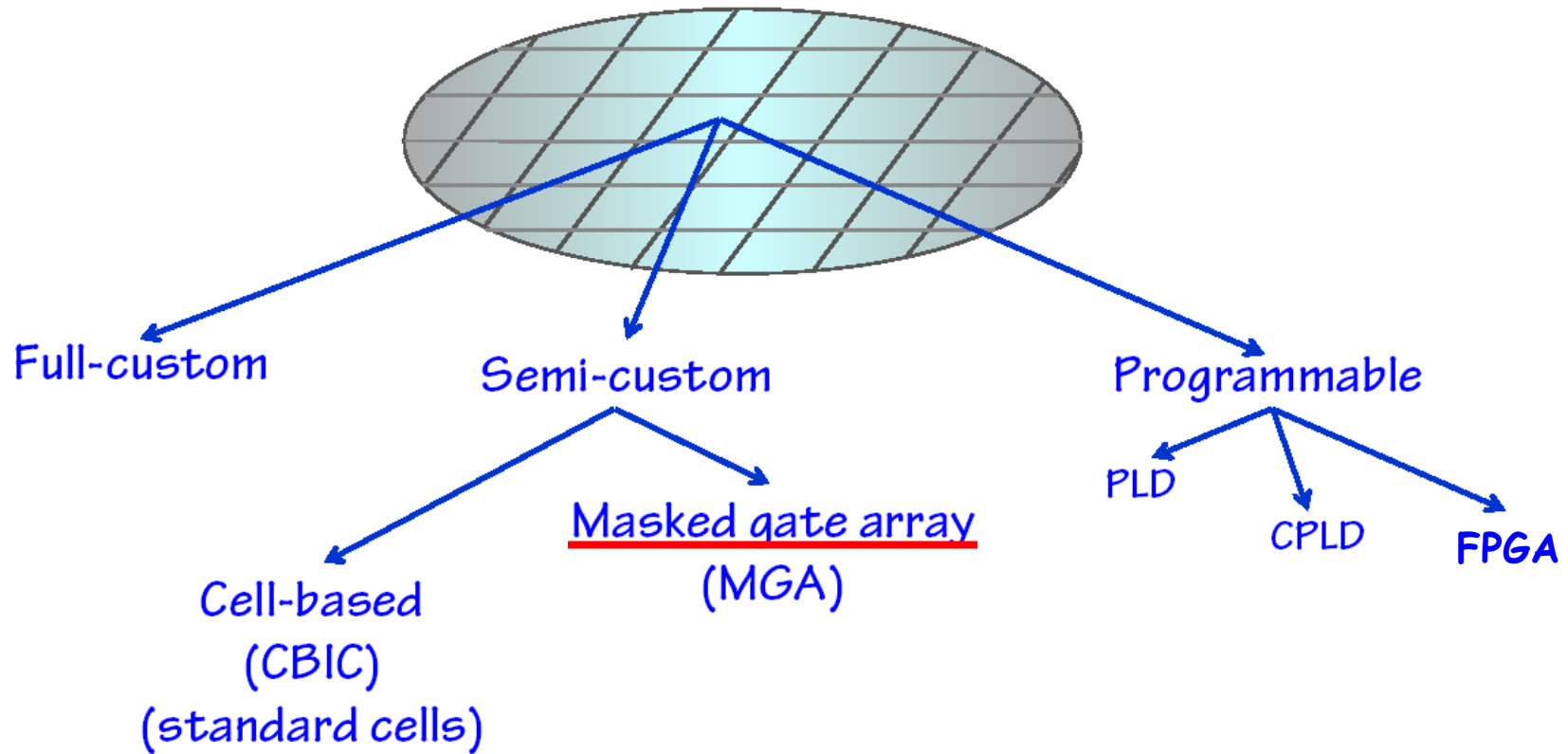
Rows of standard cells with routing channels between them

Memory array

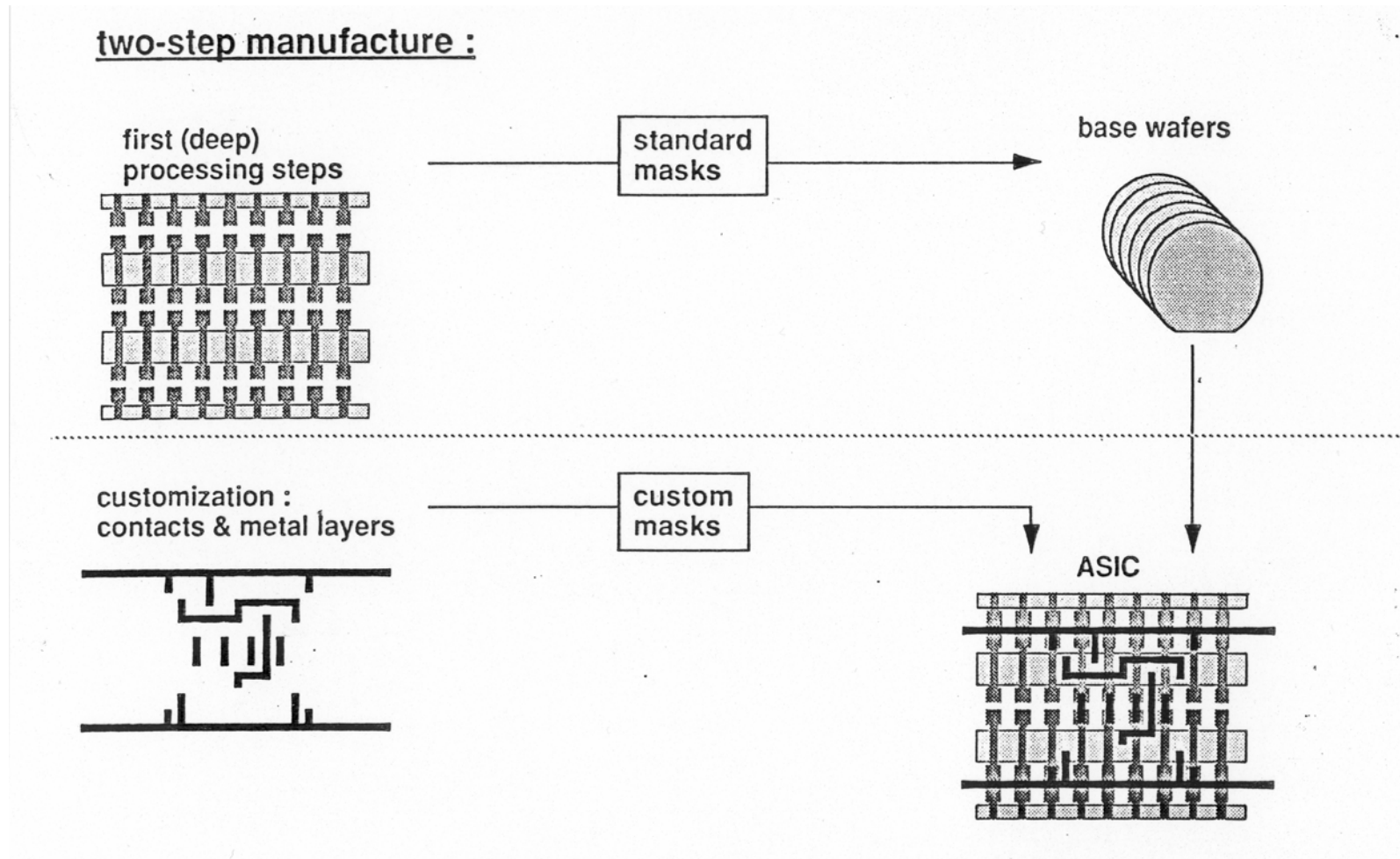
Standard Cells



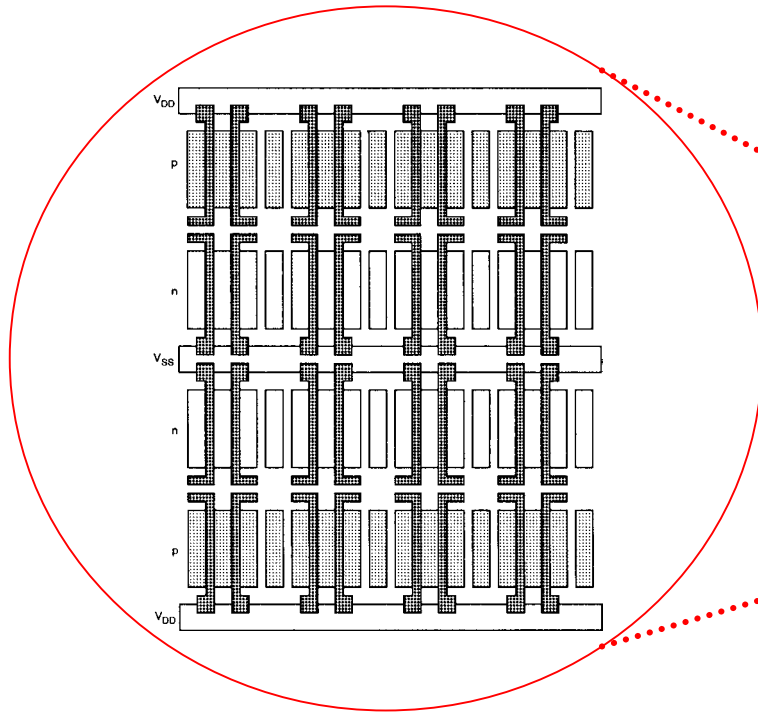
VLSI Design Styles



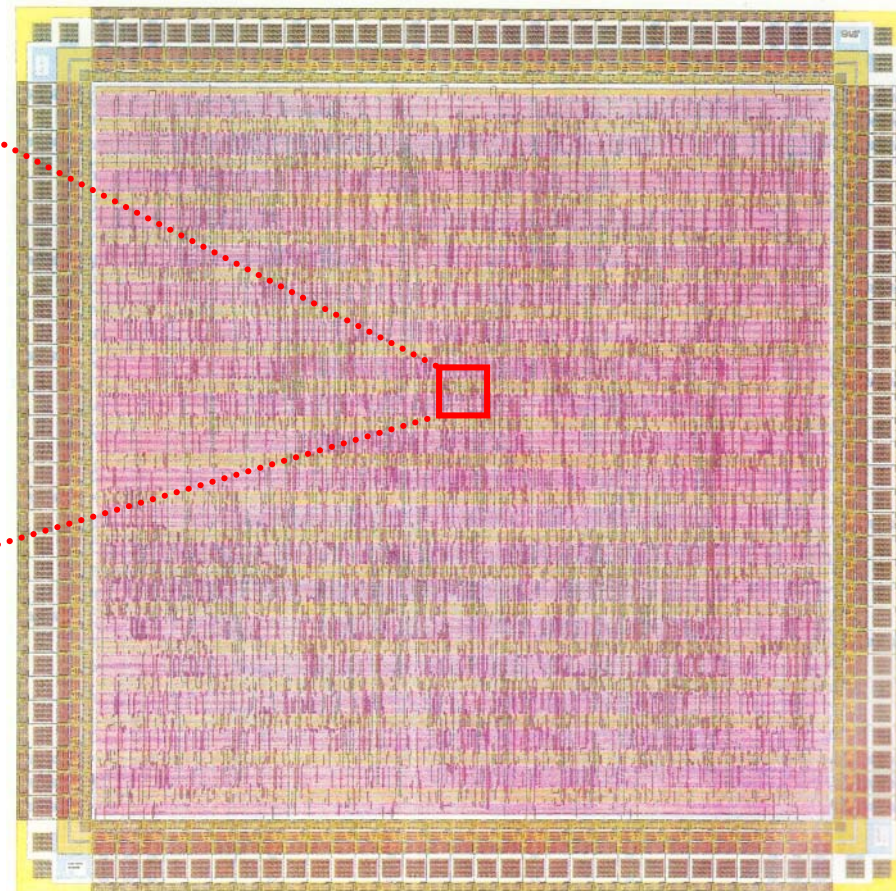
Mask Gate Array



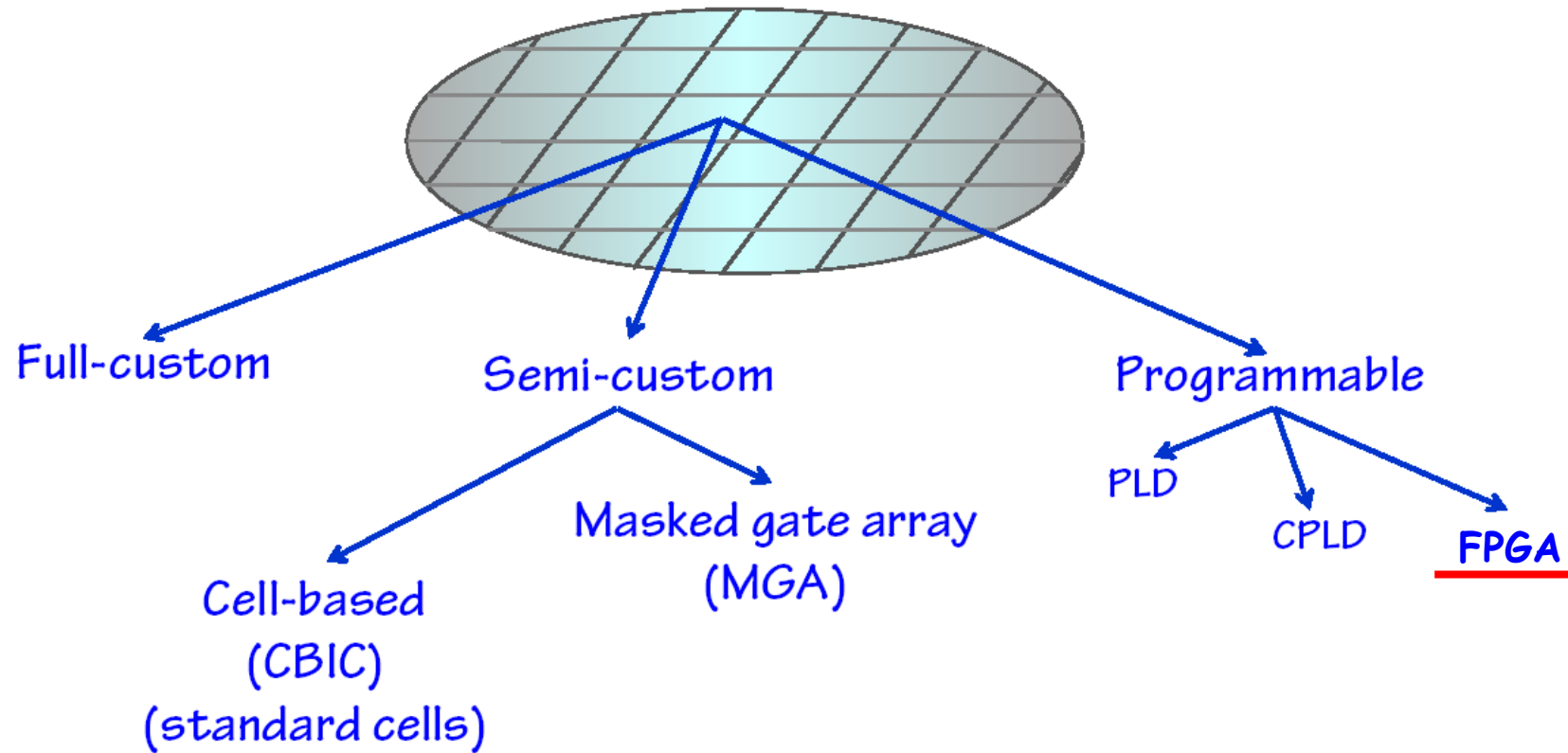
Mask Gate Array



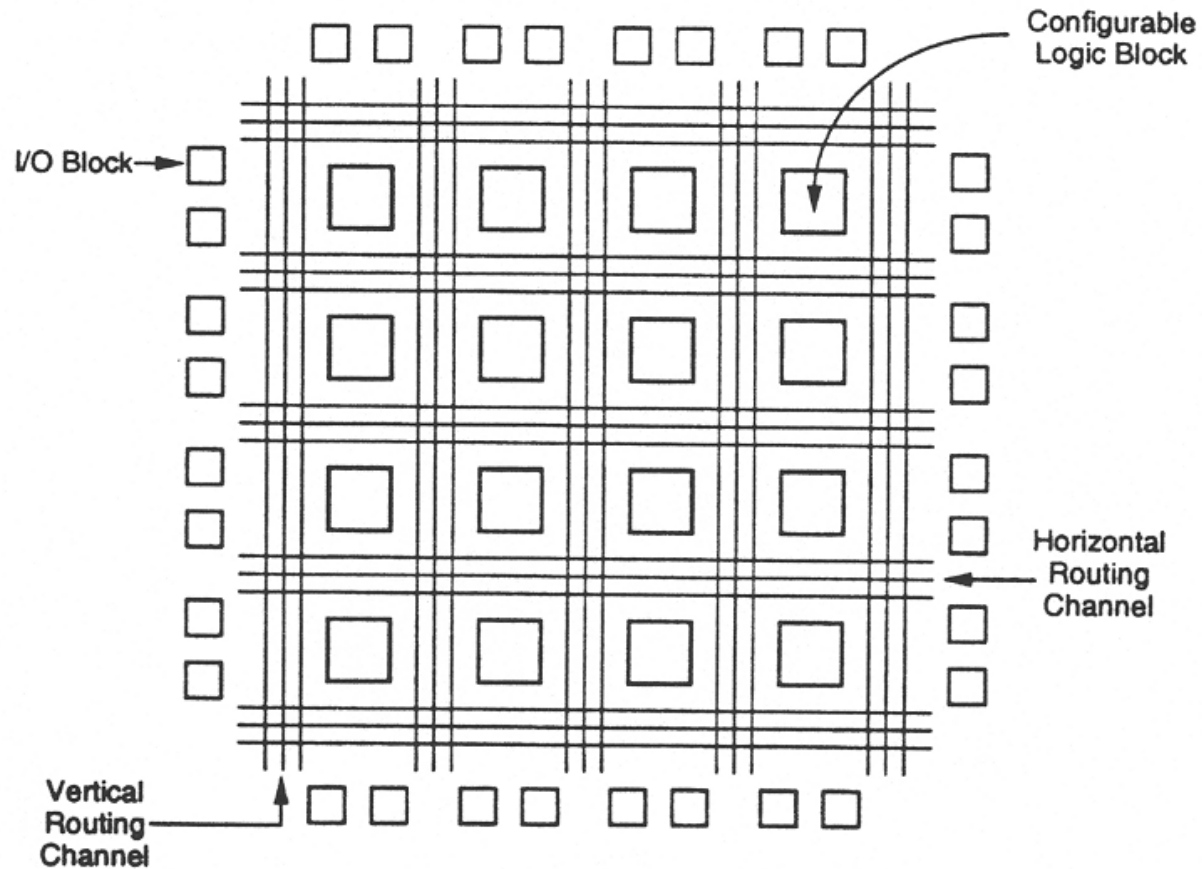
Before customization



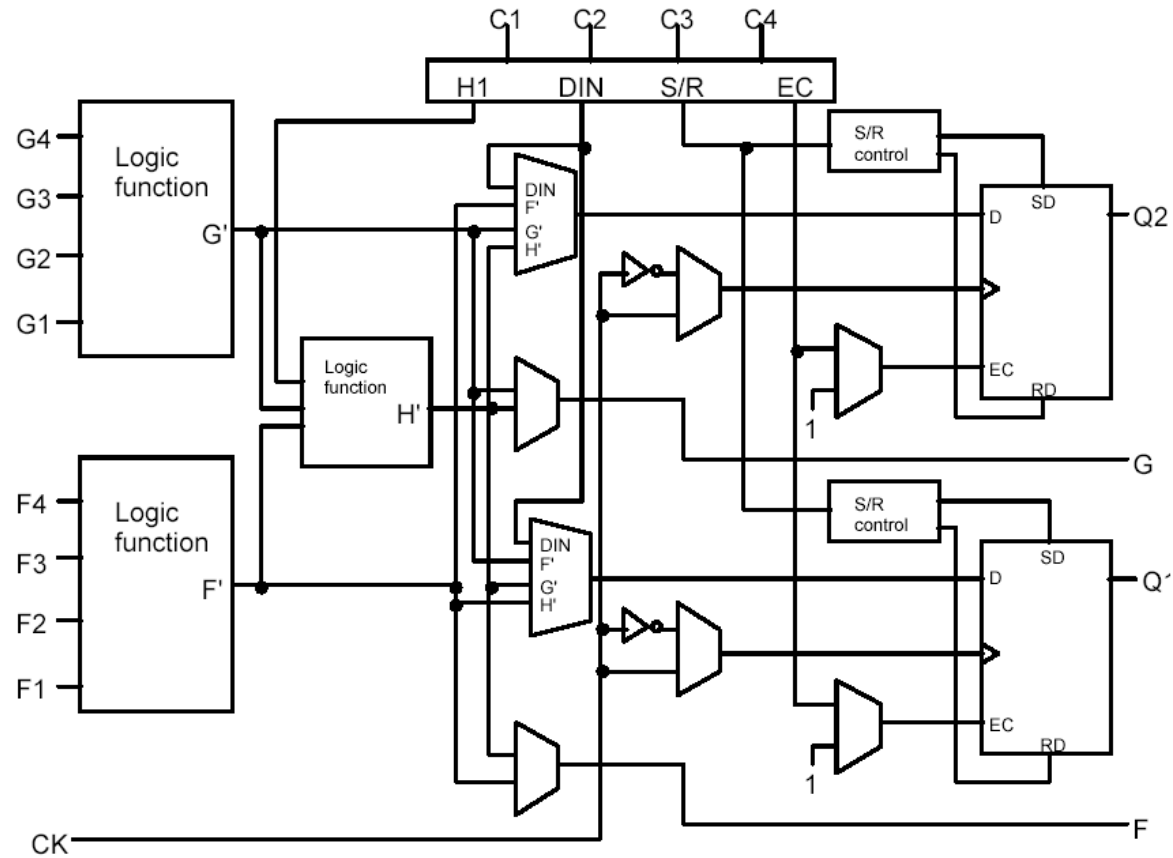
VLSI Design Styles



Field Programmable Gate Array

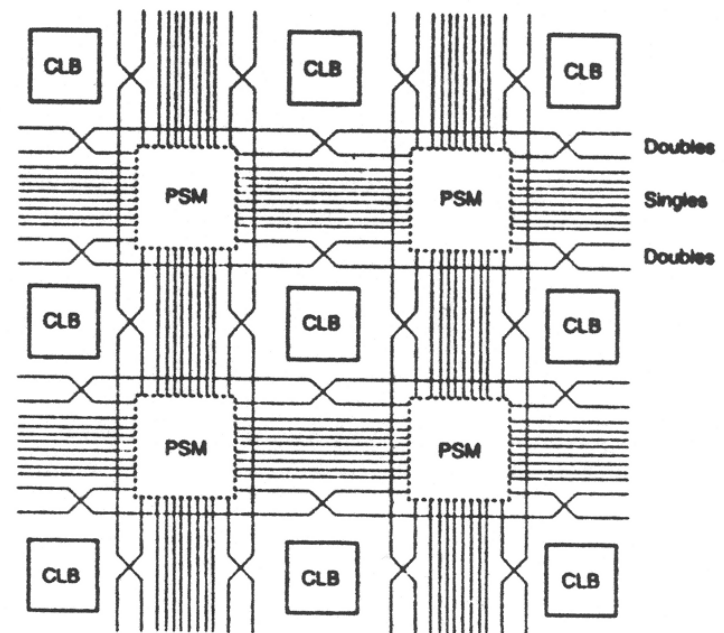
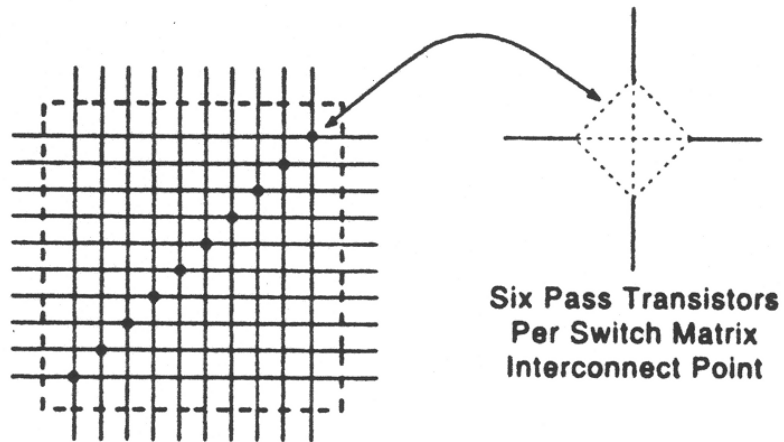


Field Programmable Gate Array



Internal structure of a CLB

Field Programmable Gate Array



1.2 Objective and Organization of the Book

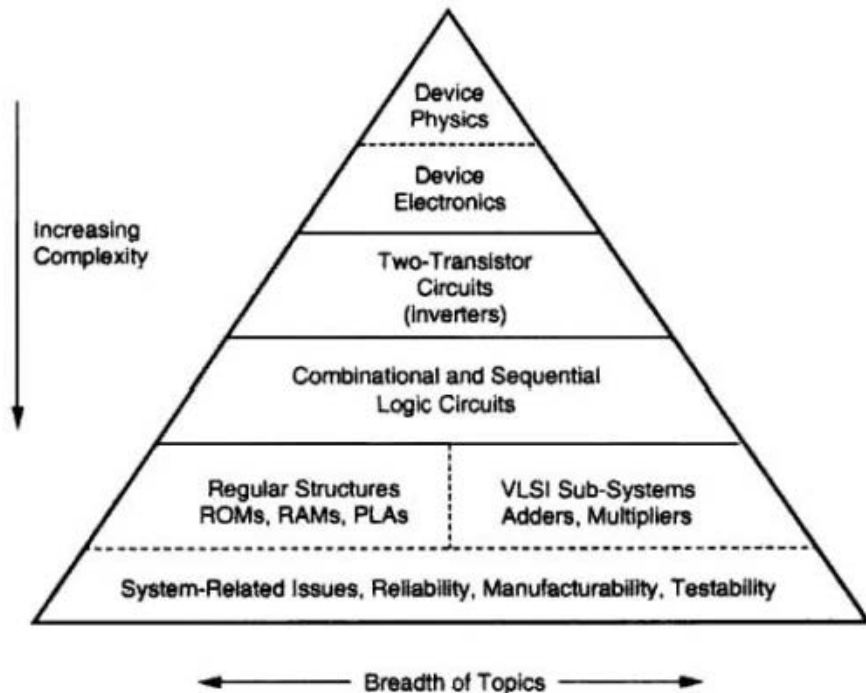


Figure 1.4. The ordering of topics covered in a typical digital integrated circuits course.

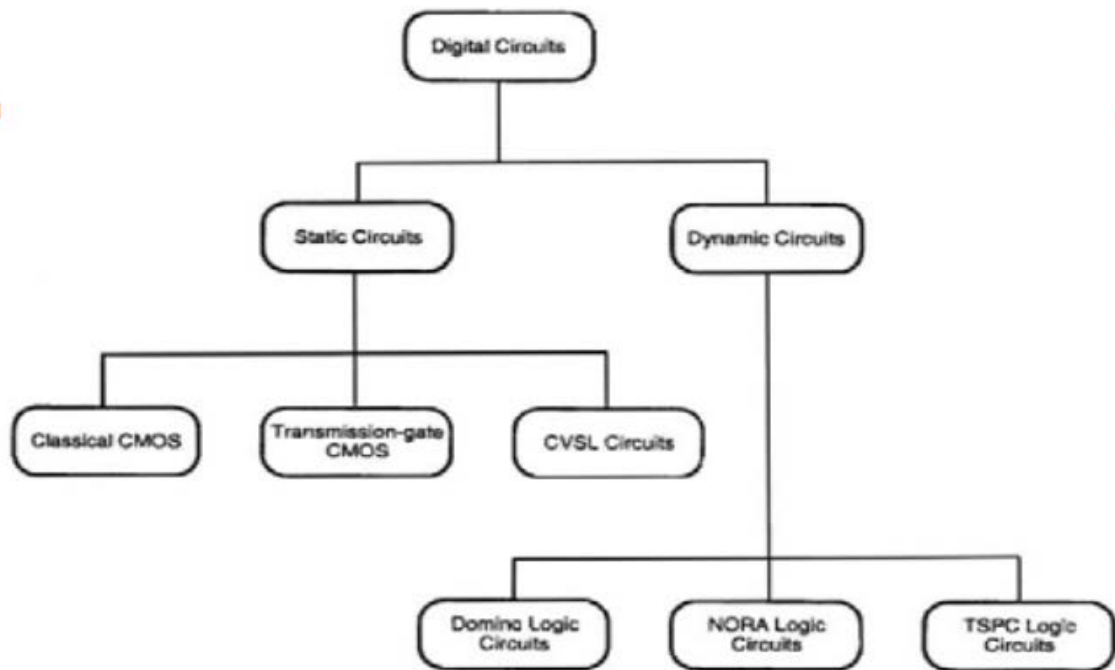


Figure 1.5. Classification of CMOS digital circuit types.

CVSL: Cascade Voltage Switch Logic

NORA: NO RACE circuits

TSPC: True-Single Phase Clock

1.3 A Circuit Design Example

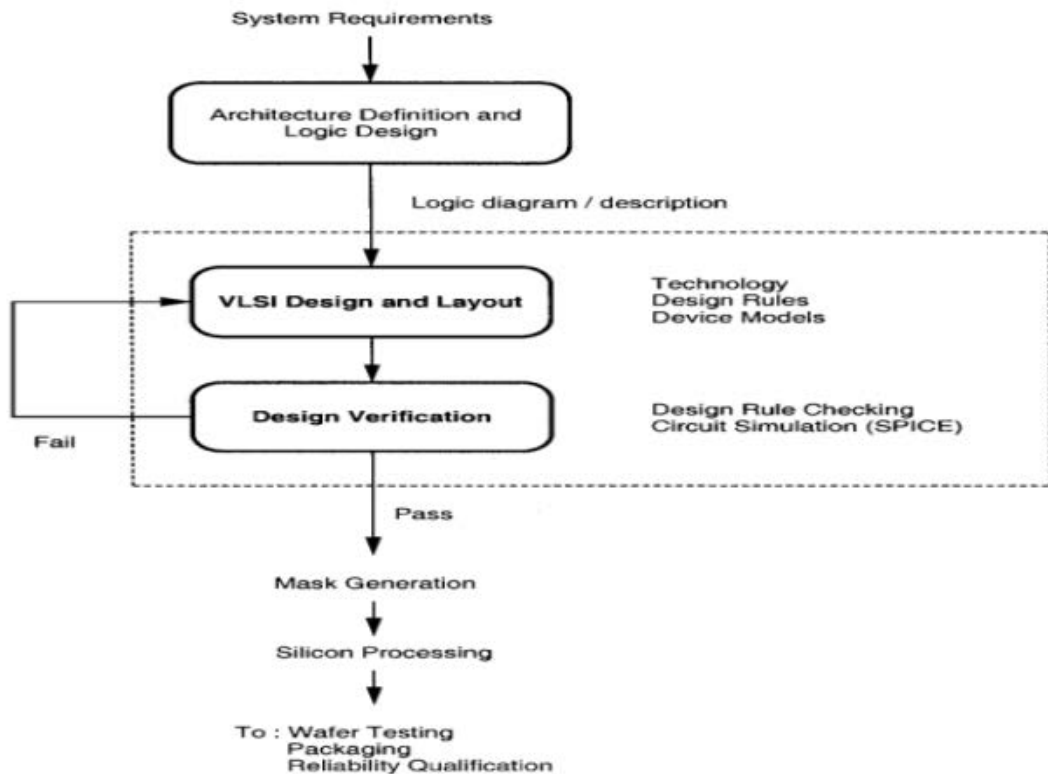
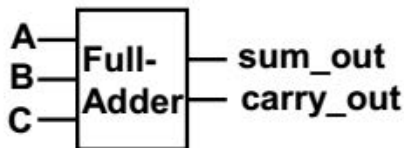


Figure 1.6 The flow of circuit design procedures.

One-bit Full-Adder Circuit Design:

Using 0.8 μ m twin-well CMOS technology with specification:

- 1) Propagation delay times of sum and carry-out signals < 1.2ns (worst)
- 2) Transition delay times of sum- and carry-out signals < 1.2ns (worst)
- 3) Circuit area < 1500 μm^2
- 4) Dynamic power dissipation (@ $V_{DD} = 5\text{V}$ and $f_{max} = 20\text{MHz}$) < 1mW



$$\begin{aligned}\text{Sum_out} &= A \oplus B \oplus C \\ &= ABC + \overline{A}\overline{B}C + \overline{A}B\overline{C} + A\overline{B}\overline{C}\end{aligned}$$

$$\text{Carry_out} = AB + AC + BC$$

$$\text{Sum_out} = ABC + (A+B+C)\text{carry_out}$$

| A | B | C | sum_out | carry_out |
|---|---|---|---------|-----------|
| 0 | 0 | 0 | 0 | 0 |
| 0 | 0 | 1 | 1 | 0 |
| 0 | 1 | 0 | 1 | 0 |
| 0 | 1 | 1 | 0 | 1 |
| 1 | 0 | 0 | 1 | 0 |
| 1 | 0 | 1 | 0 | 1 |
| 1 | 1 | 0 | 0 | 1 |
| 1 | 1 | 1 | 1 | 1 |

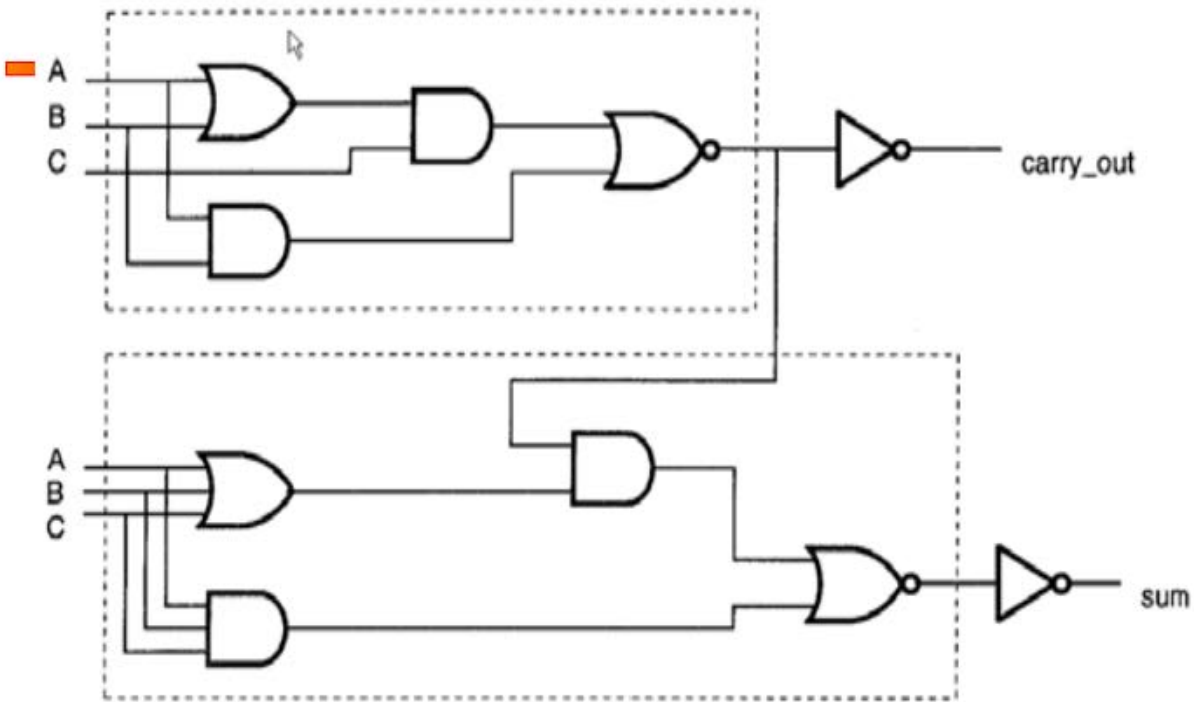


Figure 1.7 Gate-level schematic of the one-bit full-adder circuit.

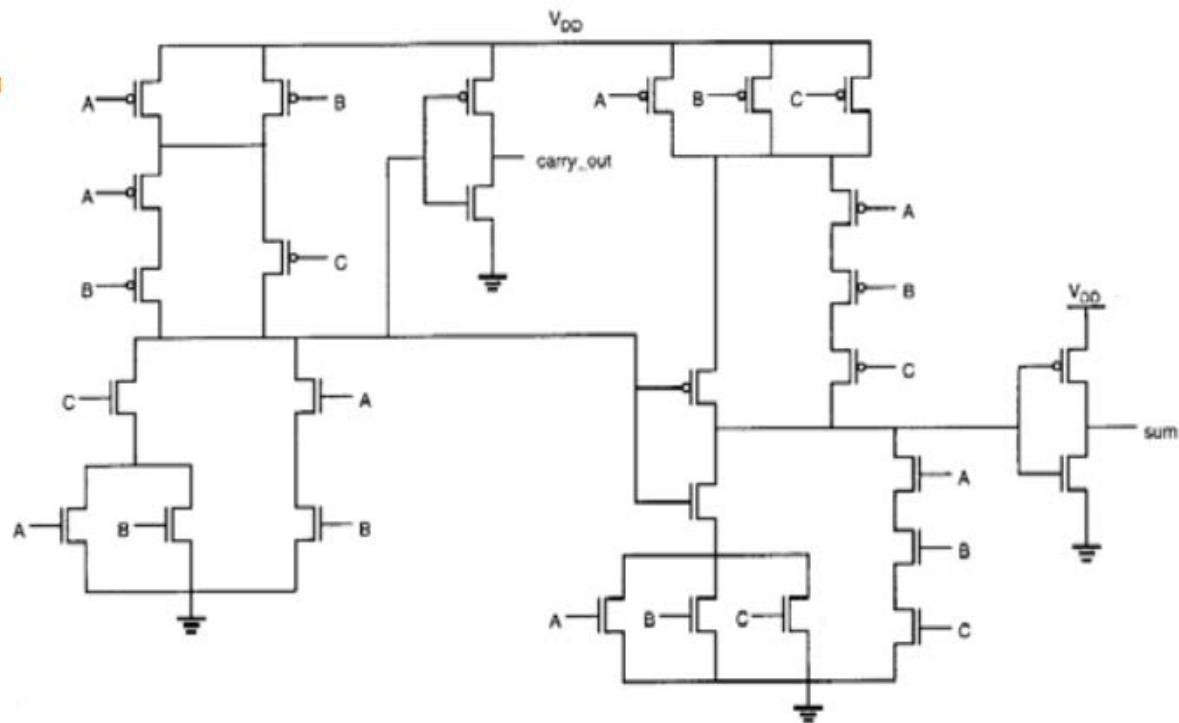


Figure 1.8 Transistor-level schematic of the one-bit full-adder circuit.

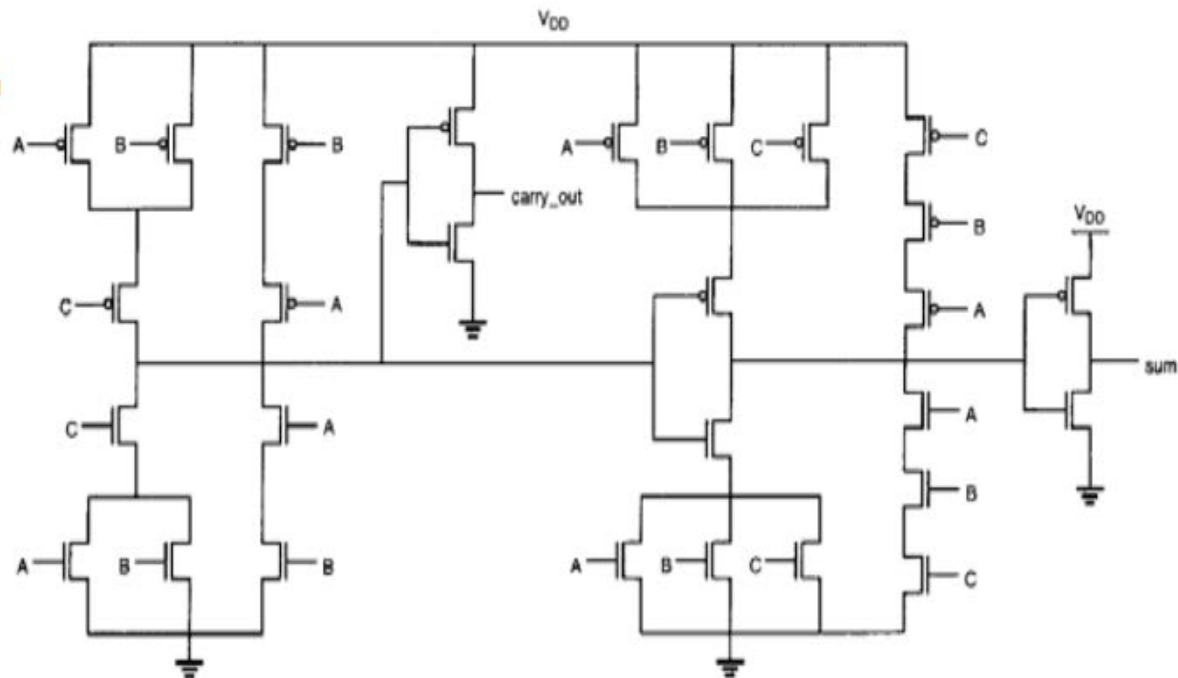
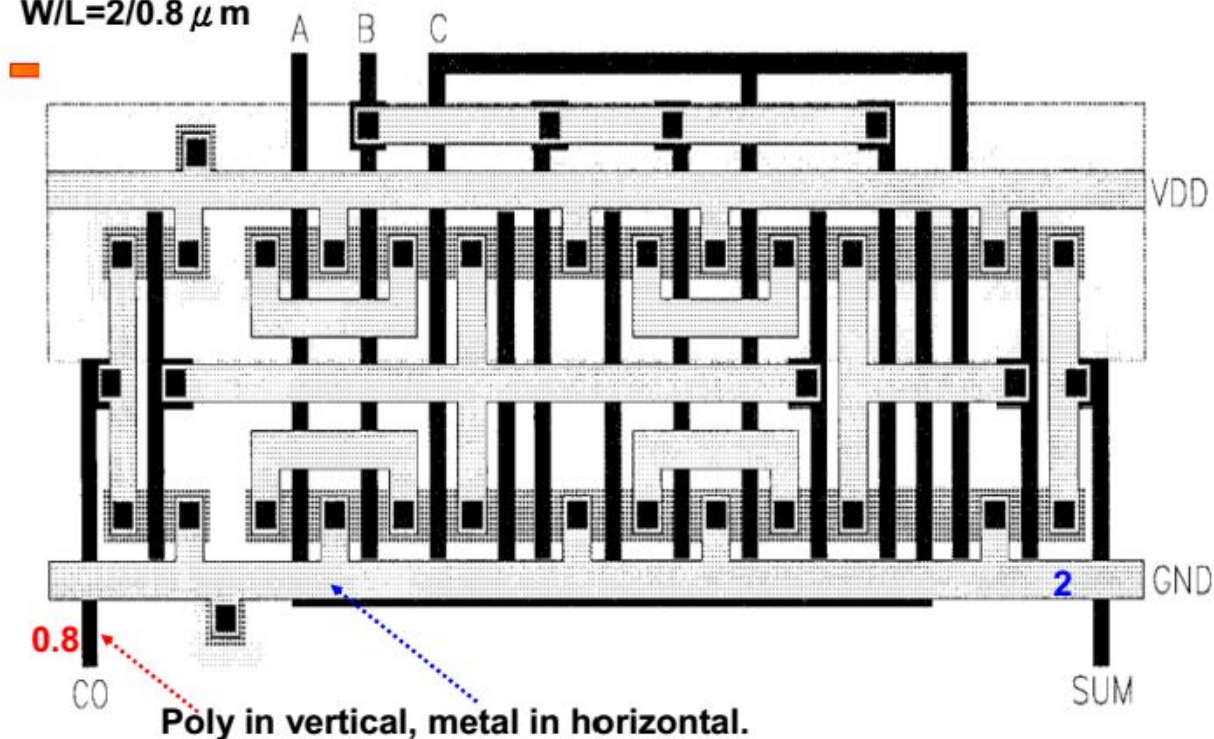


Figure 1.9 Alternate transistor-level schematic of the one-bit full-adder circuit (note that the nMOS and pMOS networks are completely symmetric).

$W/L=2/0.8 \mu m$



Poly in vertical, metal in horizontal.

Figure 1.10 Initial layout of the full-adder circuit using minimum-size transistors.

Area = $21 \times 54 \mu m^2 = 1134 \mu m^2$

SPICE simulation

Minimum Size Full Adder, Extracted

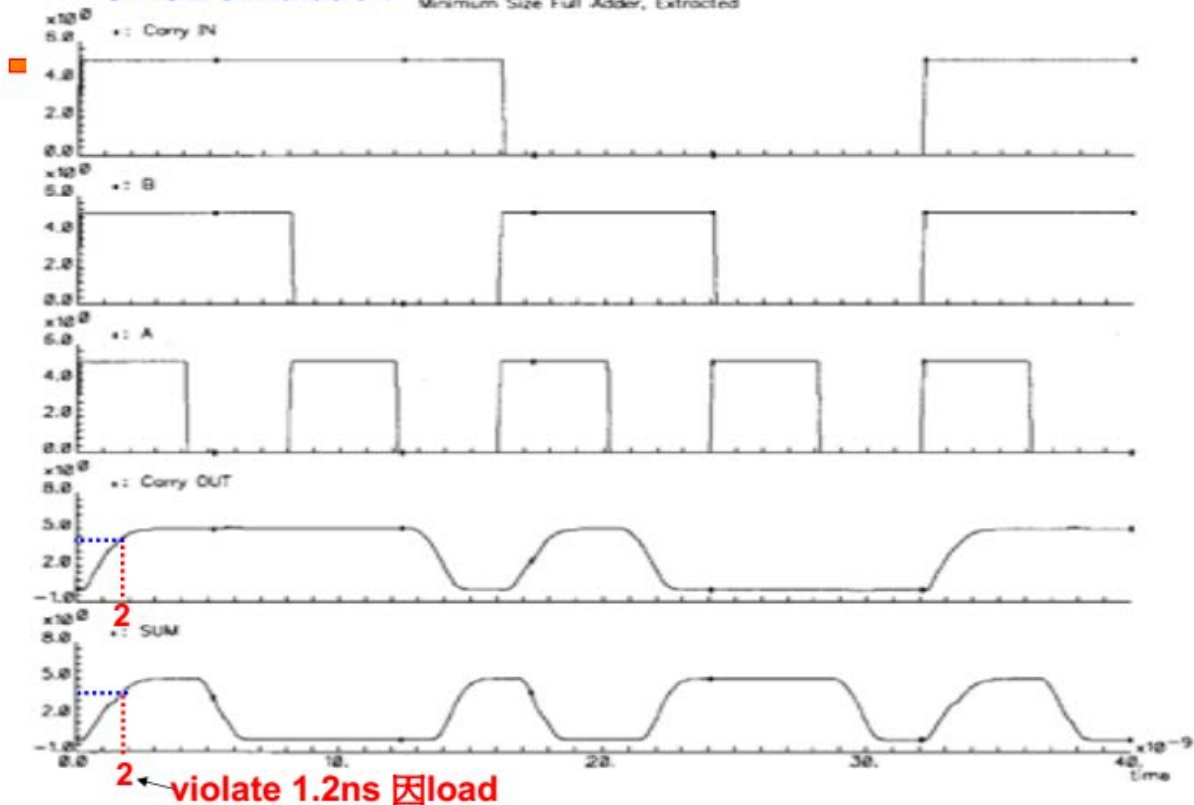


Figure 1.11 Simulated input and output waveforms of the full-adder circuit.

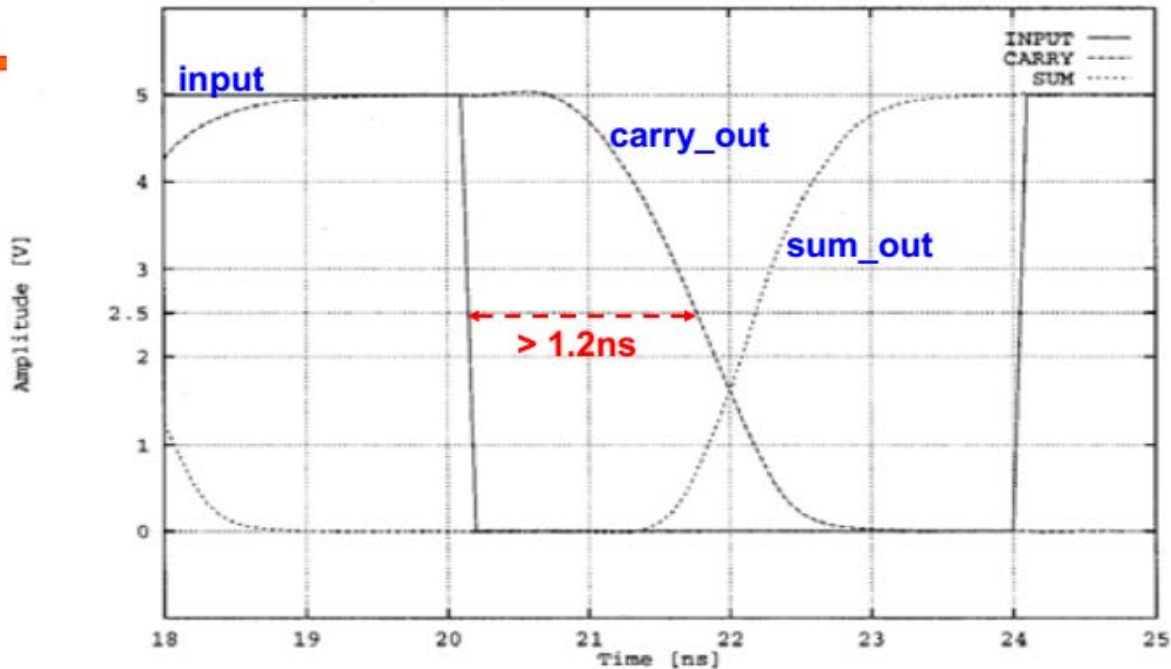
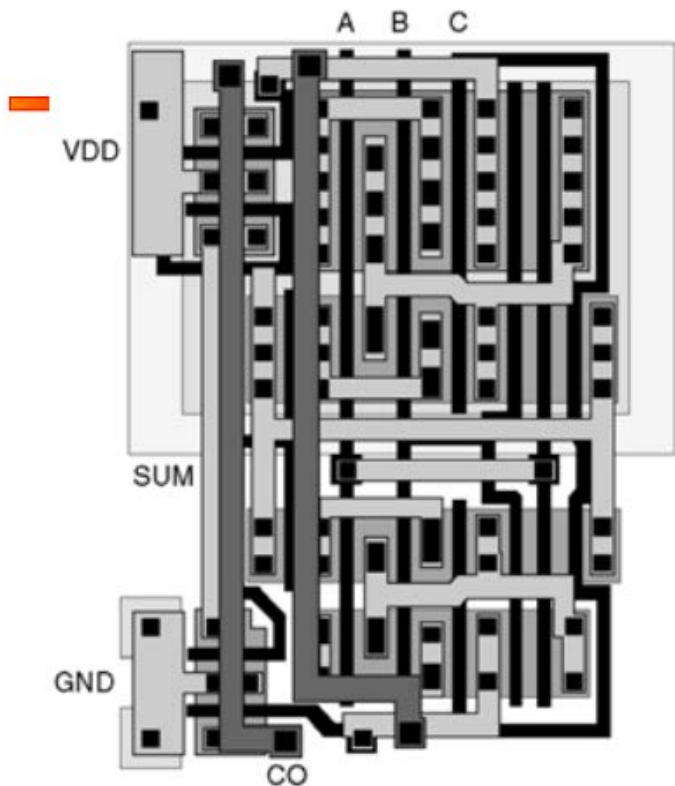


Figure 1.12 Simulated output waveforms of the full adder circuit with minimum transistor dimensions, showing the signal propagation delay during one of the worst-case transitions.



Area = 43X30 μm^2 = 1290 μm^2

- DIFF.
- NWELL
- P+
- POLY
- MET-1
- MET-2

Figure 1.13 Modified layout of the full-adder circuit, with optimized transistor dimensions.

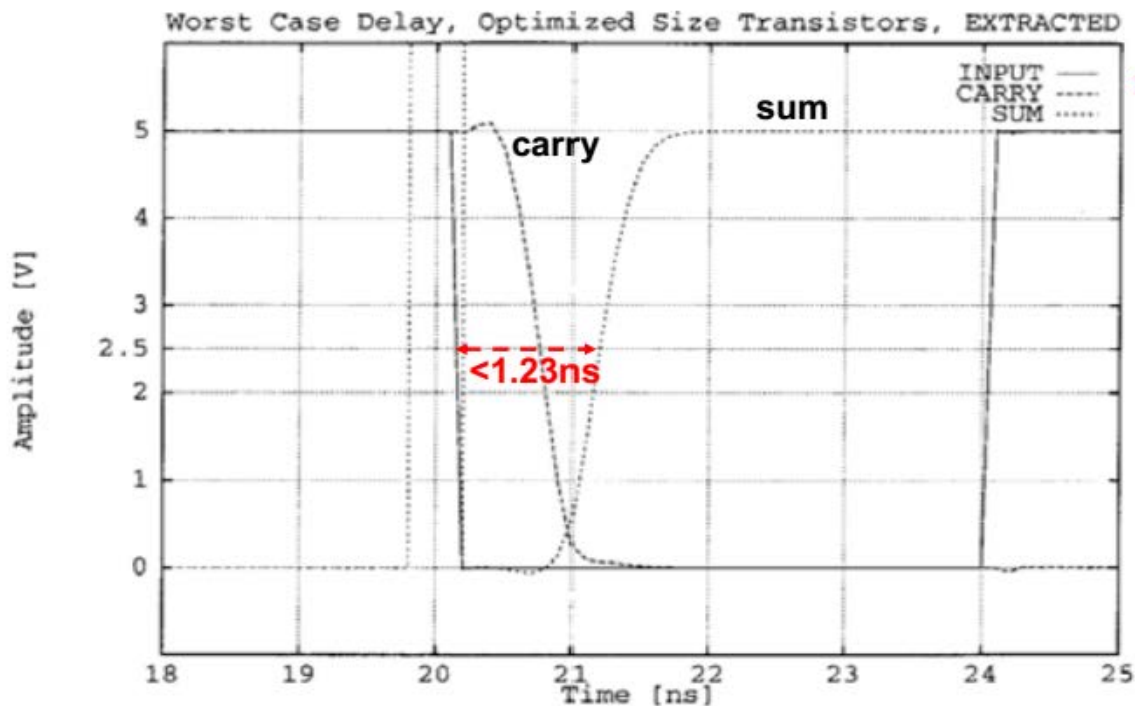


Figure 1.14 Simulated output waveforms of the full-adder circuit with optimized transistor dimensions, showing the signal propagation delay during the same worst-case transition.

Power dissipation = $460\ \mu\text{W}$

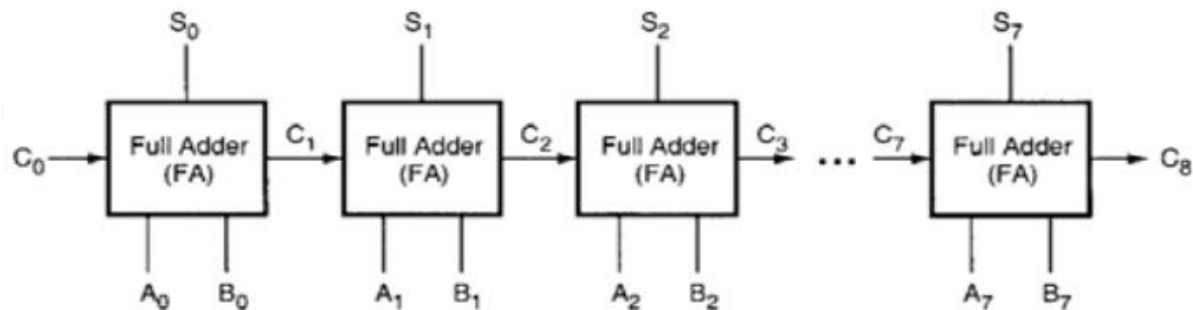


Figure 1.15 Block diagram of a carry ripple adder chain consisting of full adders.

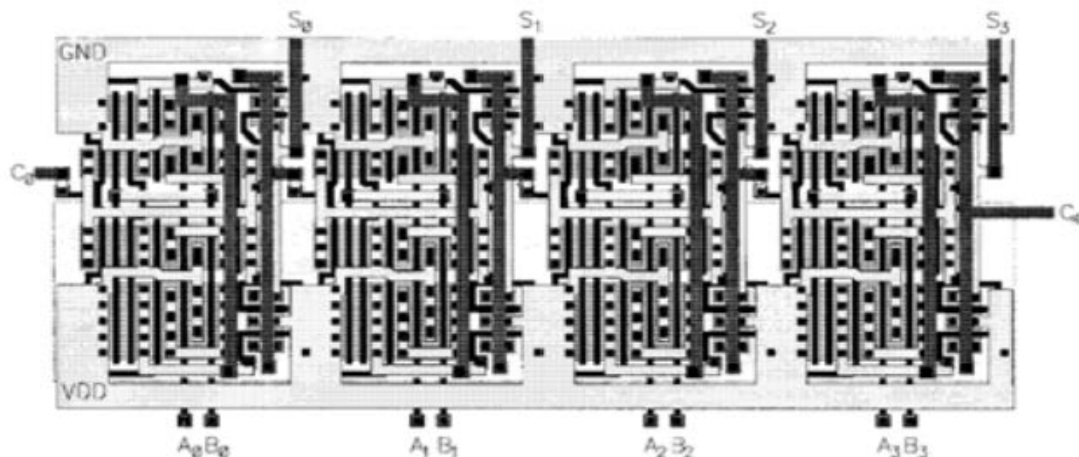


Figure 1.16 Mask layout of the 4-bit carry ripple adder array.

